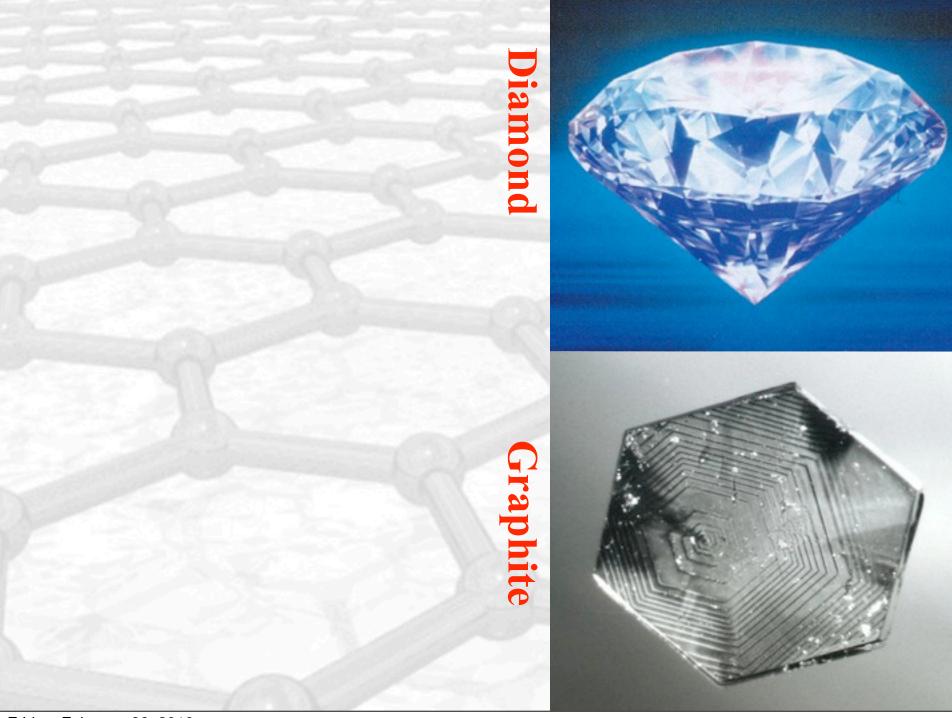
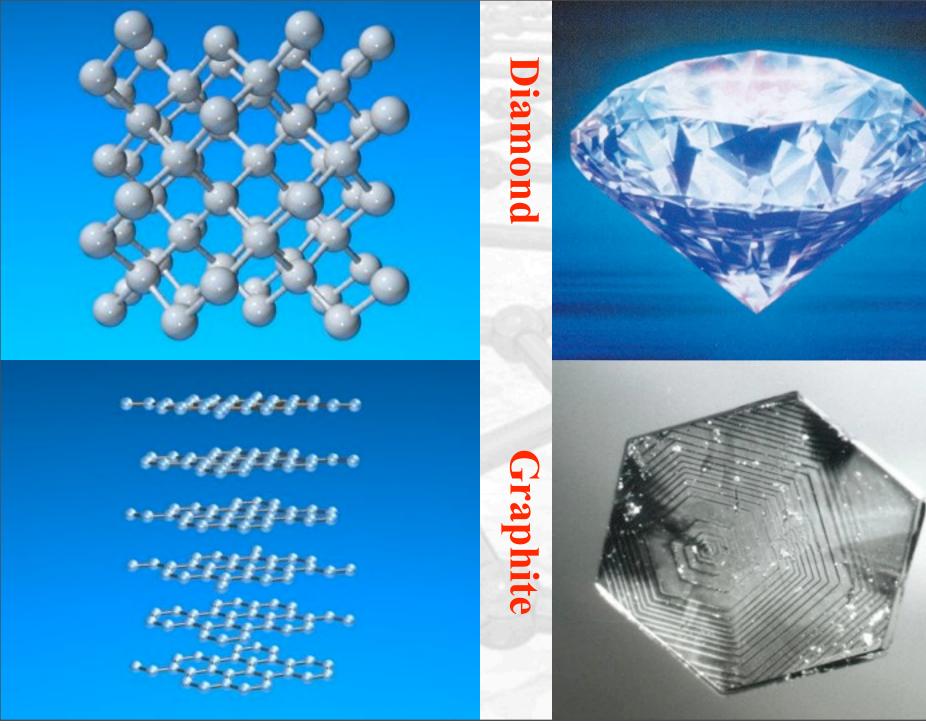


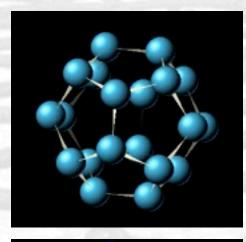
Friday, February 26, 2010



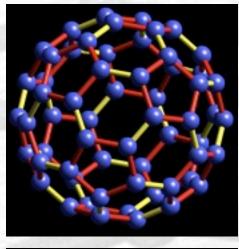
Friday, February 26, 2010



Friday, February 26, 2010

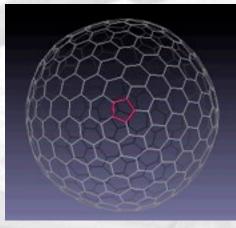


C20

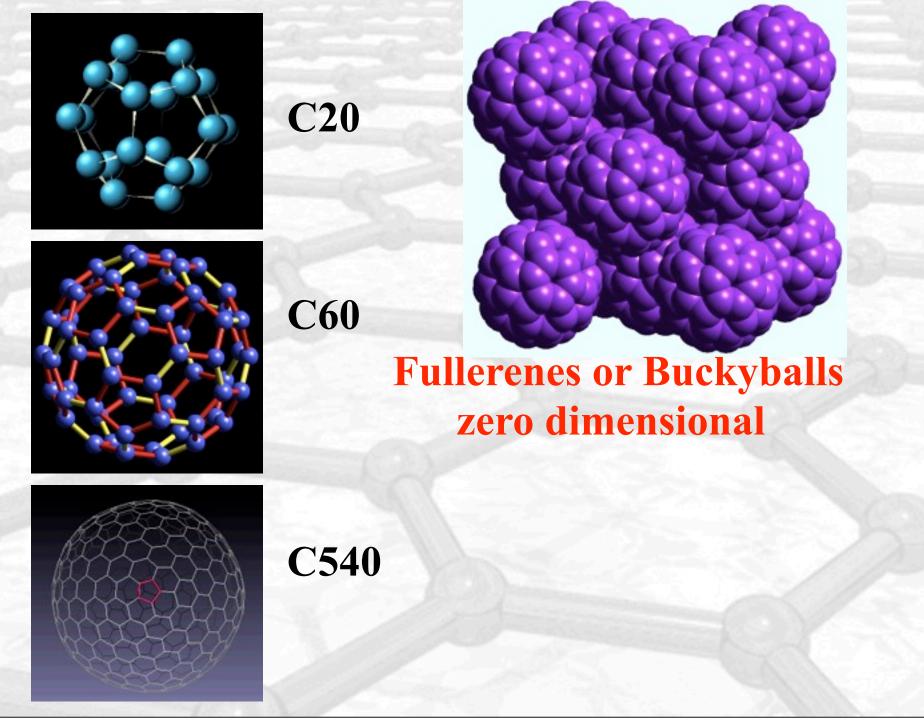


C60

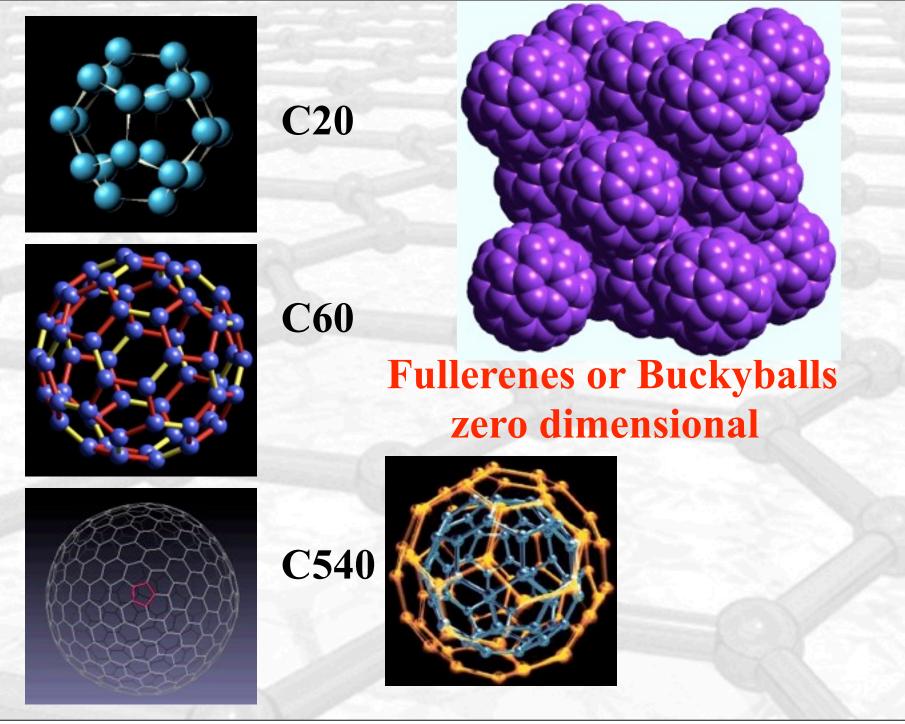
Fullerenes or Buckyballs zero dimensional

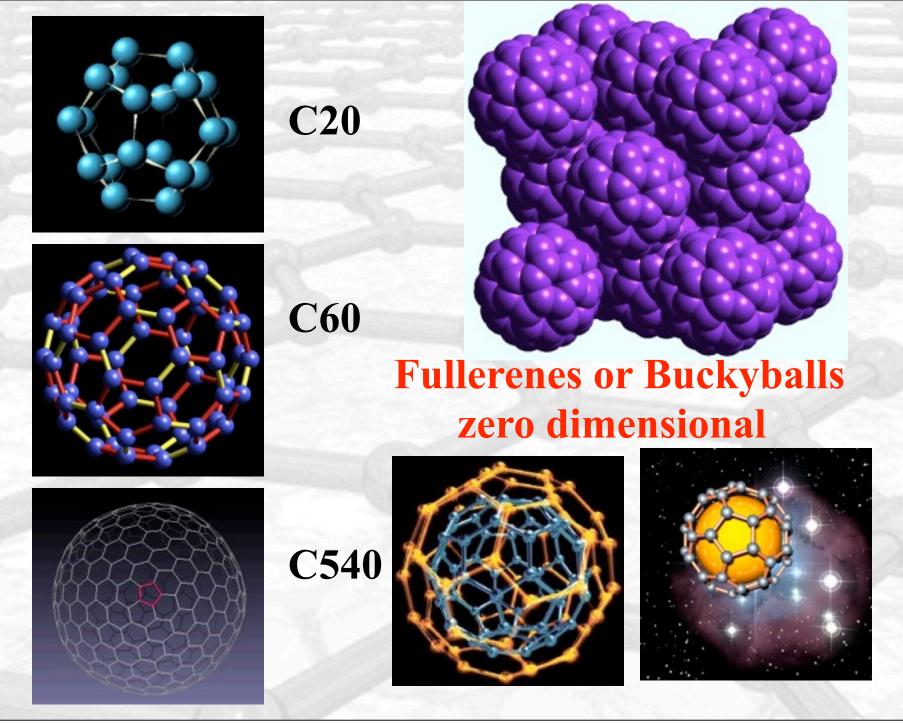


C540

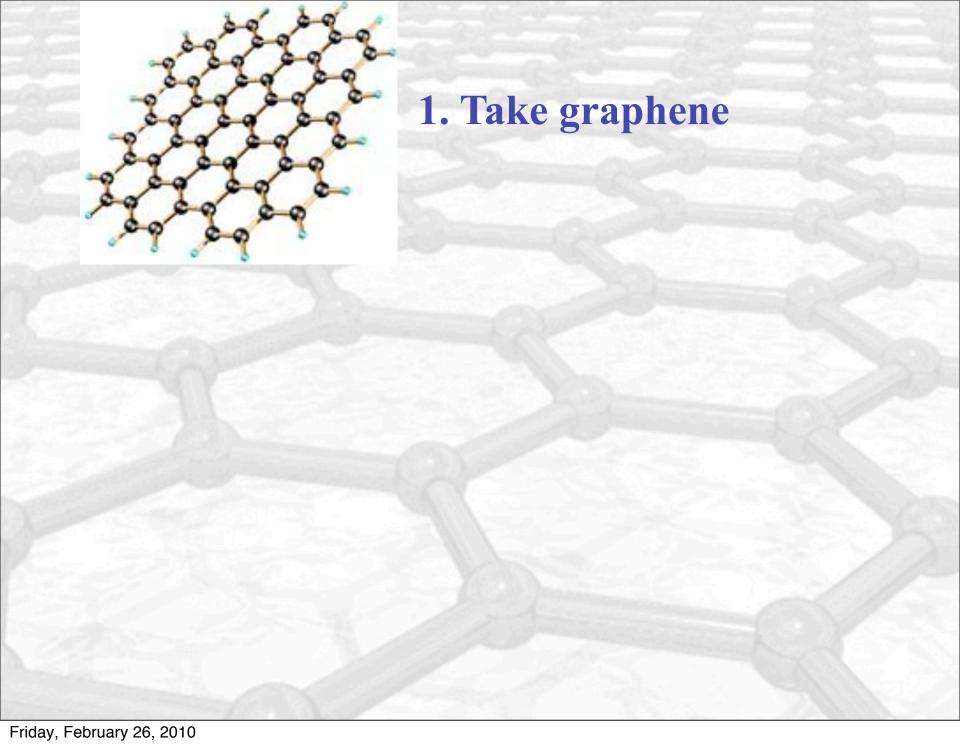


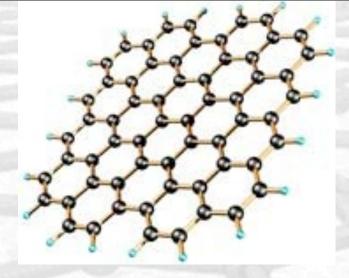
Friday, February 26, 2010



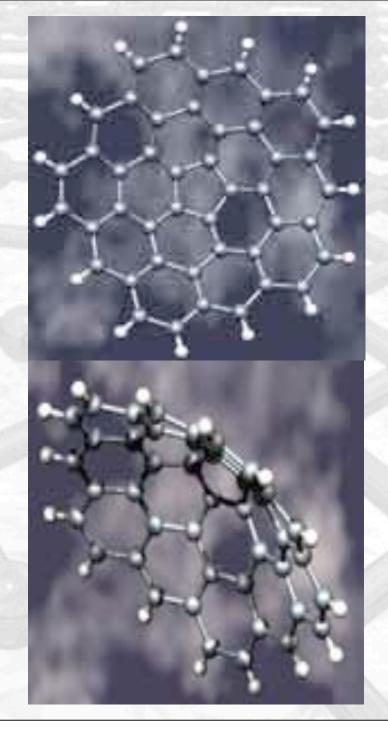


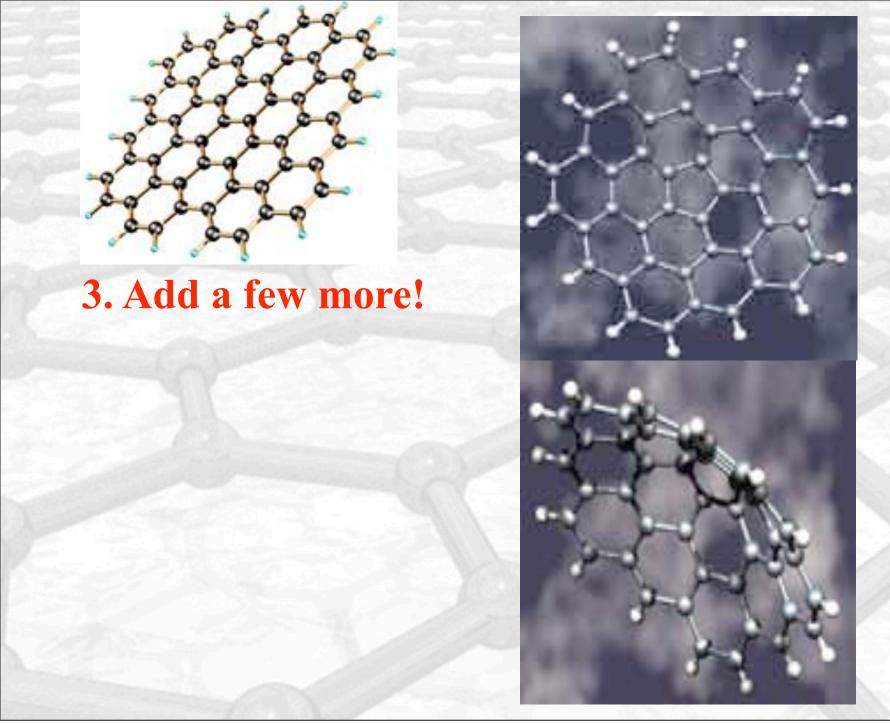


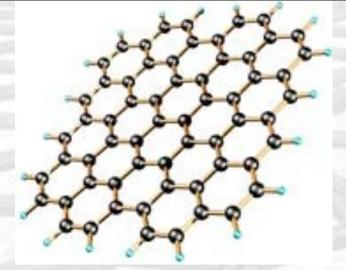




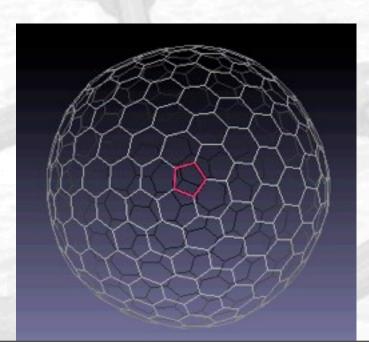
2. Add a pentagon

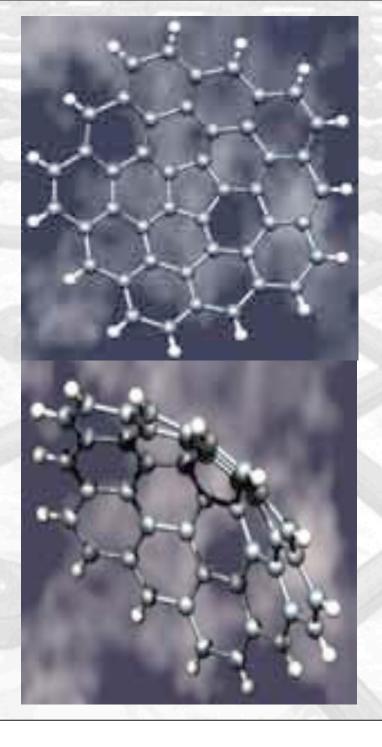


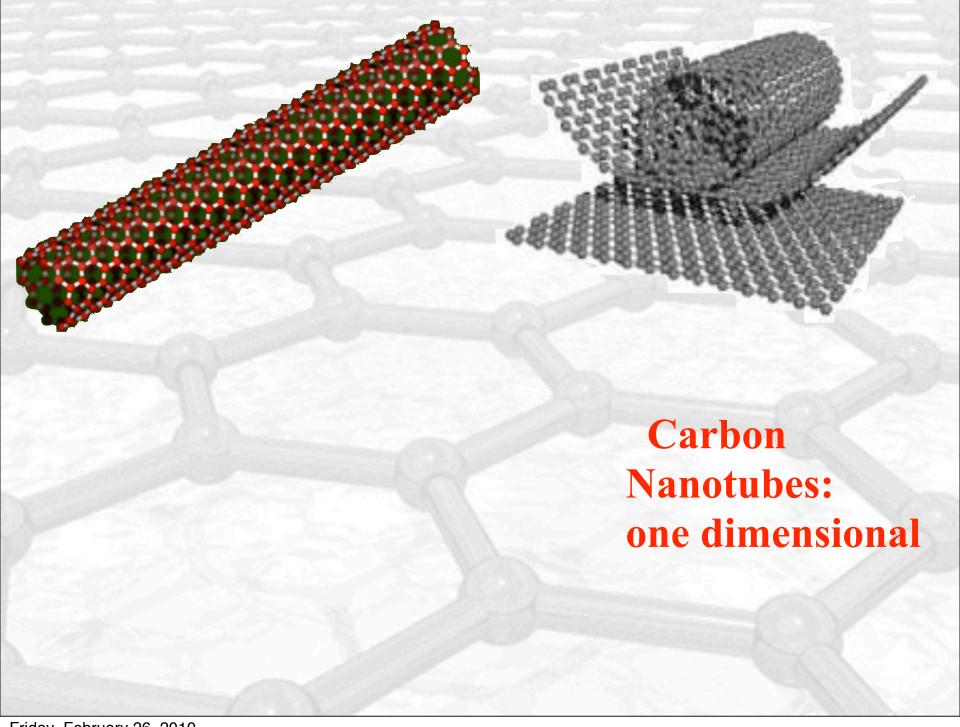


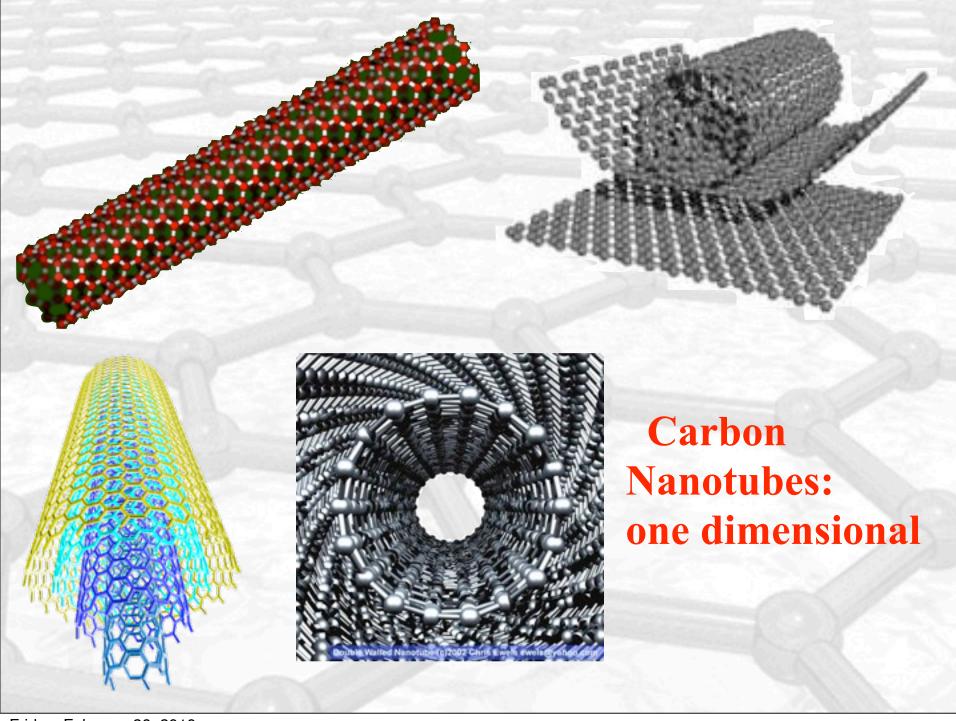


3. Add a few more!







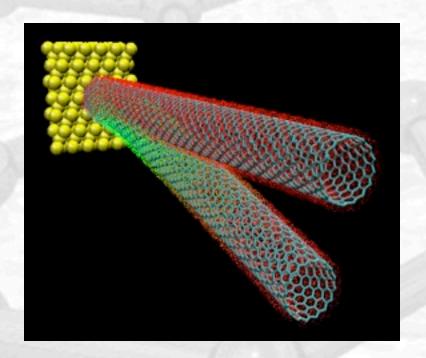


Beautiful... and useful!

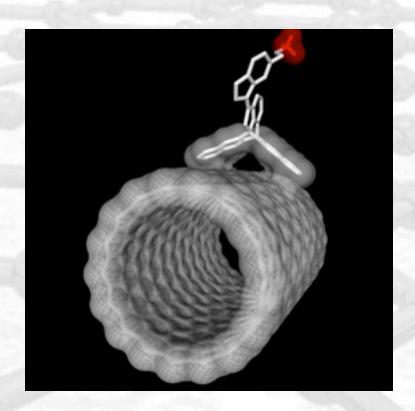




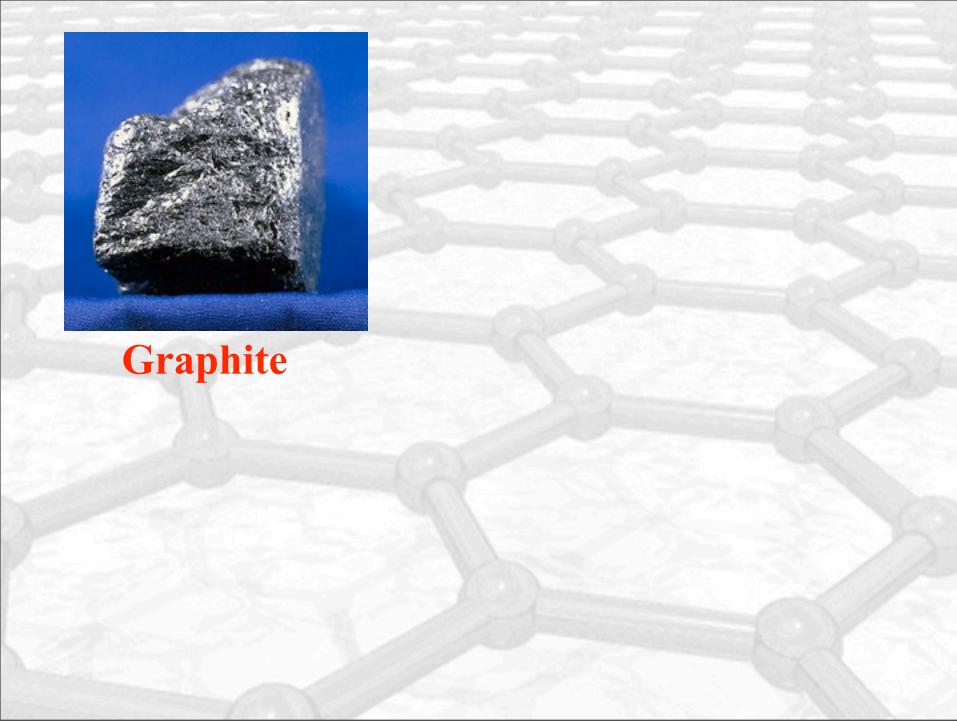
Friday, February 26, 2010



Beautiful... and useful!

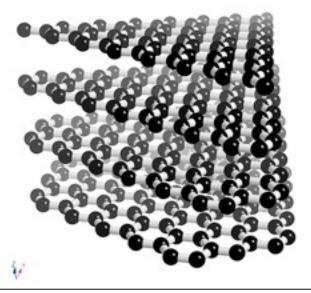


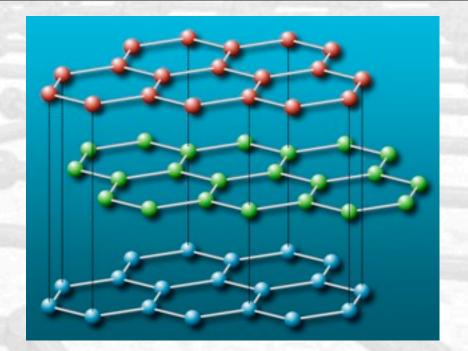
Microscopic electric cables Nanomechanical Resonator Chemical sensors

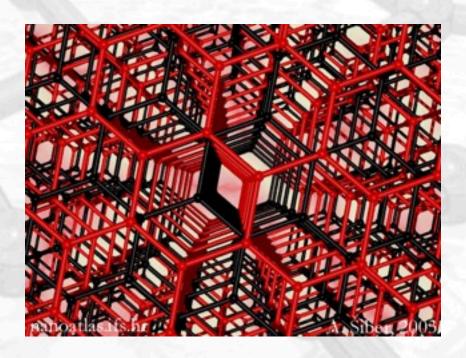




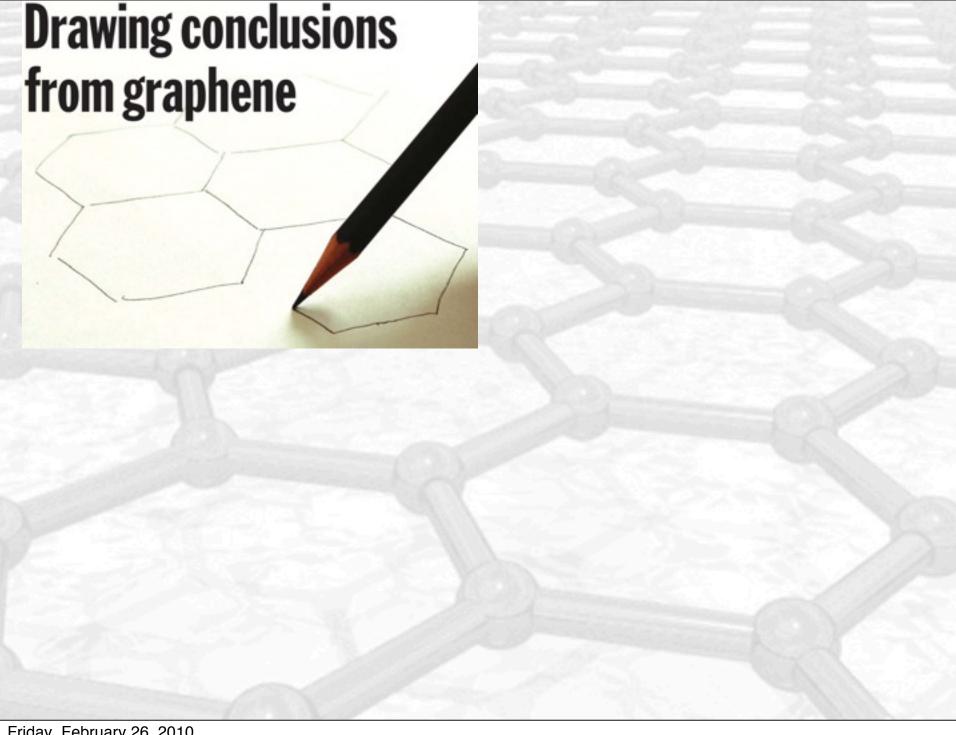
Graphite Stacked graphene!

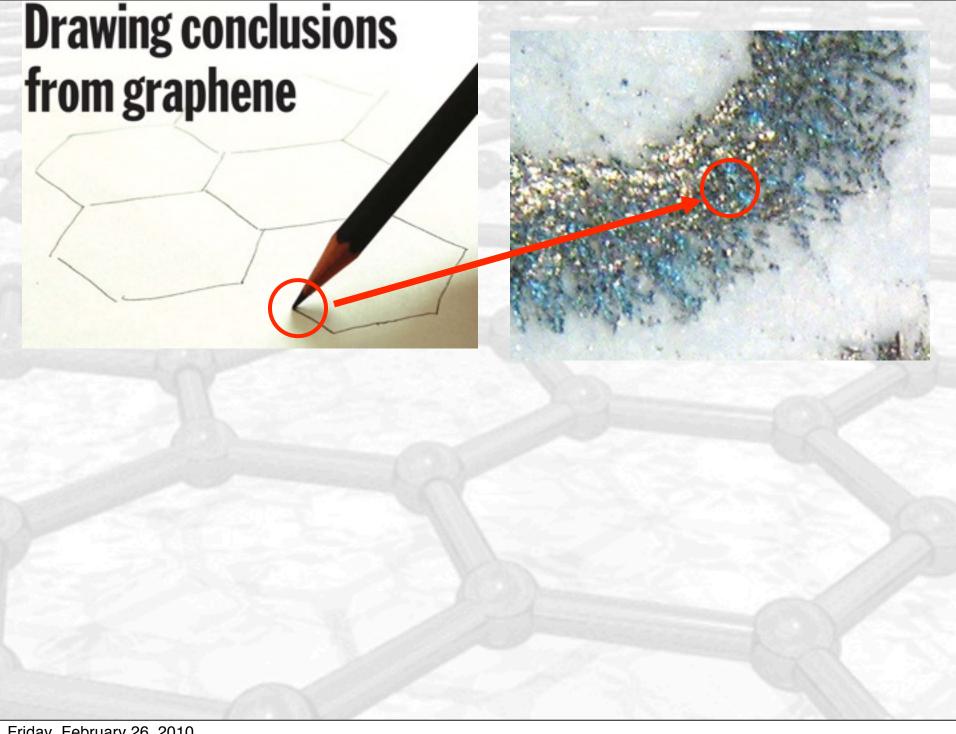


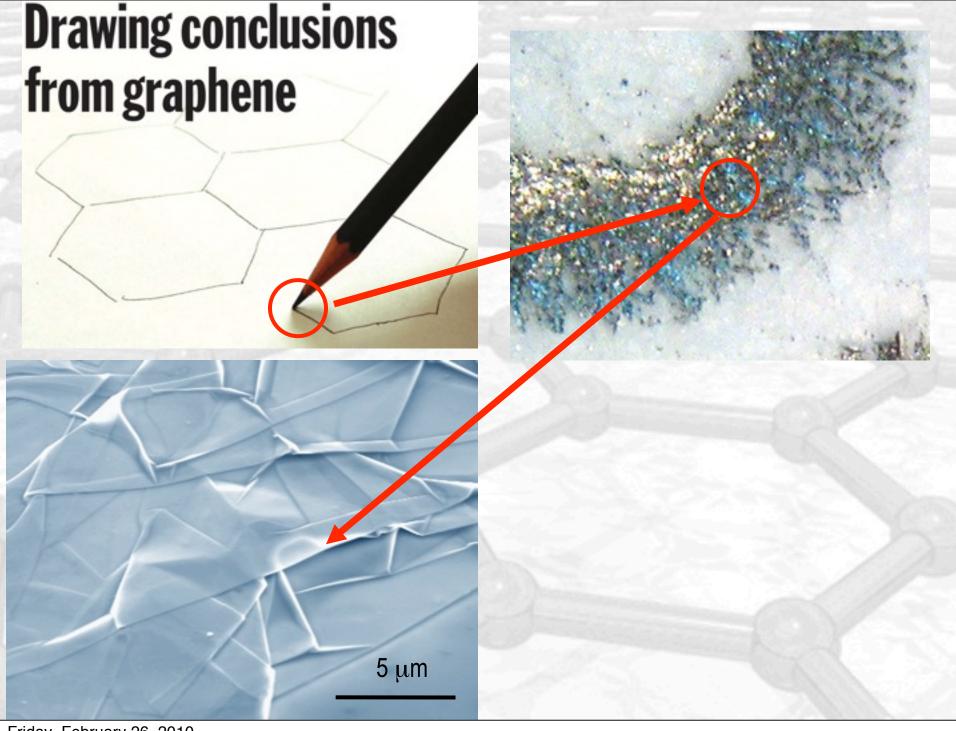




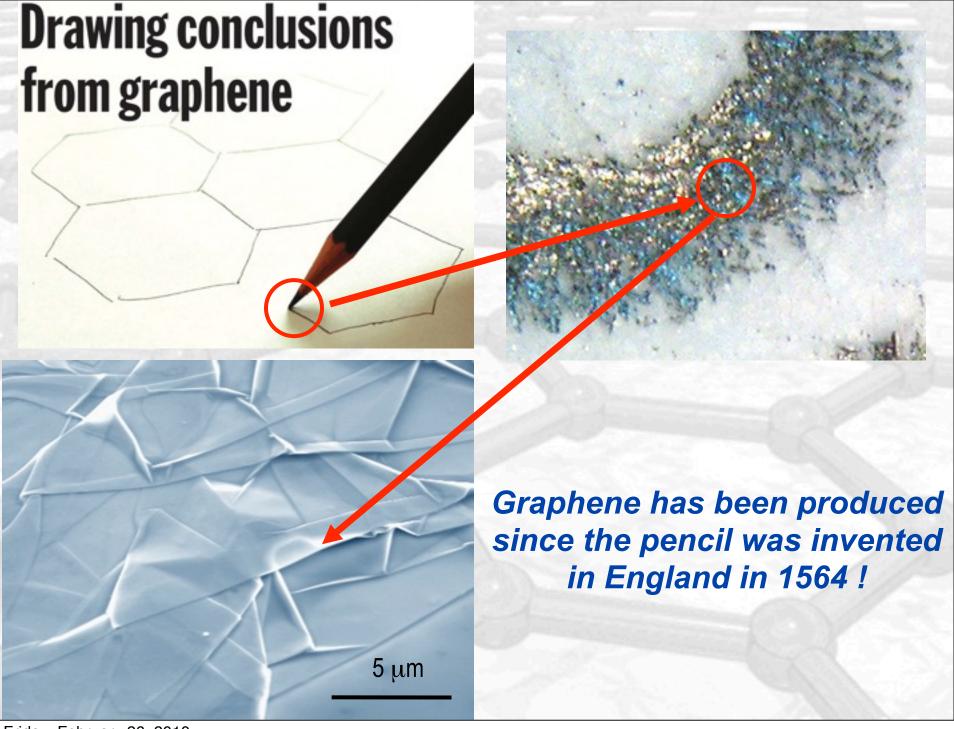
Friday, February 26, 2010







Friday, February 26, 2010



From 1564 to 2004!

Electric Field Effect in Atomically Thin Carbon Films

K. S. Novoselov, A. K. Geim, S. V. Morozov, D. Jiang, Y. Zhang, S. V. Dubonos, L. V. Grigorieva, A. A. Firsov

We describe monocrystalline graphitic films, which are a few atoms thick but are nonetheless stable under ambient conditions, metallic, and of remarkably high quality. The films are found to be a two-dimensional semimetal with a tiny overlap between valence and conductance bands, and they exhibit a strong ambipolar electric field effect such that electrons and holes in concentrations up to 10¹³ per square centimeter and with room-temperature mobilities of ~ 10,000 square centimeters per volt-second can be induced by applying gate voltage.

The ability to control electronic properties of a material by externally applied voltage is at the heart of modern electronics. In many cases, it is the electric field effect that allows one to vary the carrier concentration in a semiconductor device and, consequently, change an electric current through it. As the semiconductor industry is nearing the limits of performance improvements for the current technologies dominated by silicon, there is a constant search for new, nontraditional materials whose properties can be controlled by the electric field. The most notable recent examples of such materials are organic conductors (I) and carbon nanotubes (2). It has long been tempting to extend the use of the field effect to metals [e.g., to develop all-metallic transistors that could be scaled down to much smaller sizes and would consume less energy and operate at higher frequencies

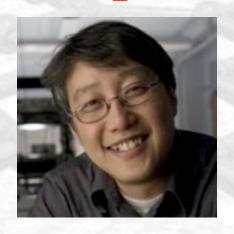
than traditional semiconducting devices (3)]. However, this would require atomically thin metal films, because the electric field is screened at extremely short distances (<1 nm) and bulk carrier concentrations in metals are large compared to the surface charge that can be induced by the field effect. Films so thin tend to be thermodynamically unstable, becoming discontinuous at thicknesses of several nanometers; so far, this has proved to be an insurmountable obstacle to metallic electronics, and no metal or semimetal has been shown to exhibit any notable (>1%) field effect (4).

We report the observation of the electric field effect in a naturally occurring twodimensional (2D) material referred to as few-layer graphene (FLG). Graphene is the name given to a single layer of carbon atoms densely packed into a benzene-ring structure, and is widely used to describe properties of many carbon-based materials, including graphite, large fullerenes, nanotubes, etc. (e.g., carbon nanotubes are usually thought of as graphene sheets rolled up into nanometer-sized cylinders) (5-7). Planar graphene itself has been presumed not to exist in the free state, being unstable with respect to the formation of curved structures such as soot, fullerenes, and nanotubes (5-14).

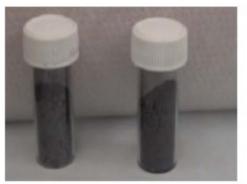
Department of Physics, University of Manchester, Manchester M13 9PL, UK. Institute for Microelectronics Technology, 142432 Chemogolovka, Russia.

^{*}To whom correspondence should be addressed. B-mail: geim@man.ac.uk

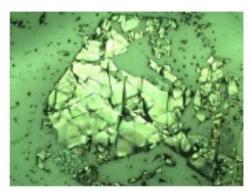
Recipe for making a graphene transistor by Philip Kim



Recipe for making a graphene transistor by Philip Kim



Graphite Flakes (Kish, Toshiba Ceramics)



Graphite Flake



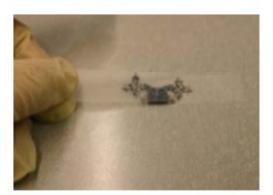
Peeling a Graphite Flake



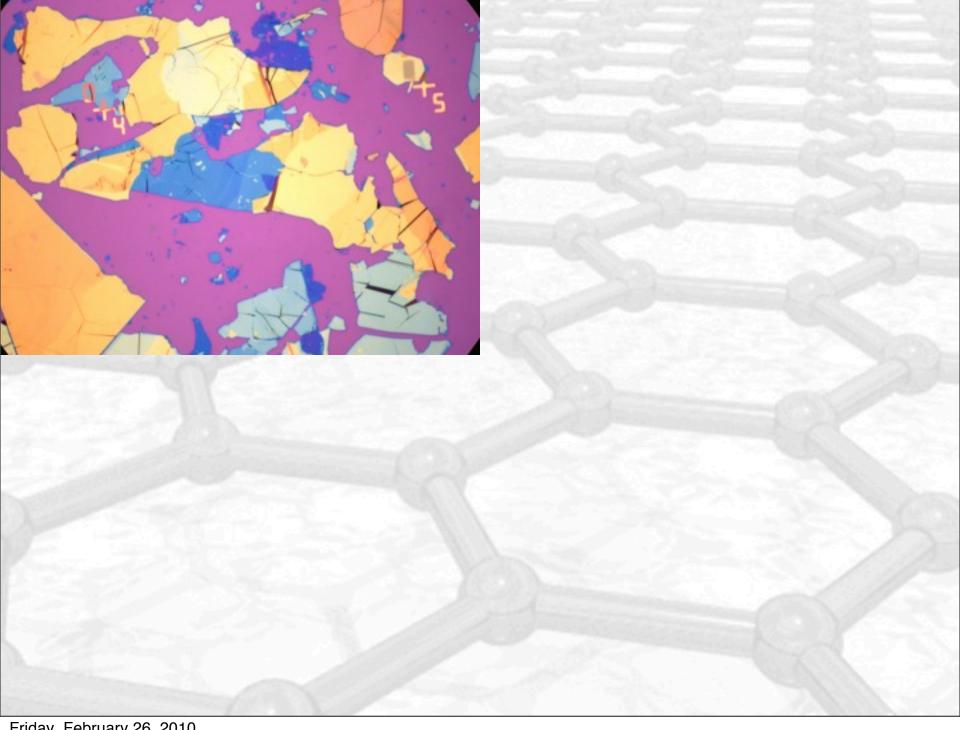
Cleaving to a SIO2/SI waver



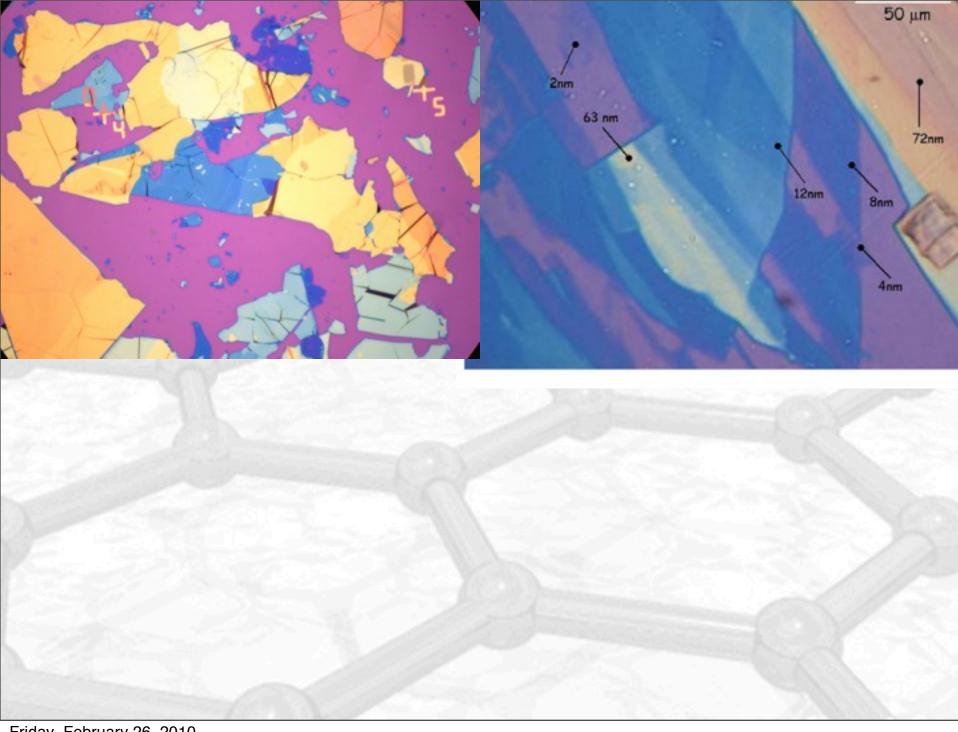
Gentle Rubbing with plastic Tweezers



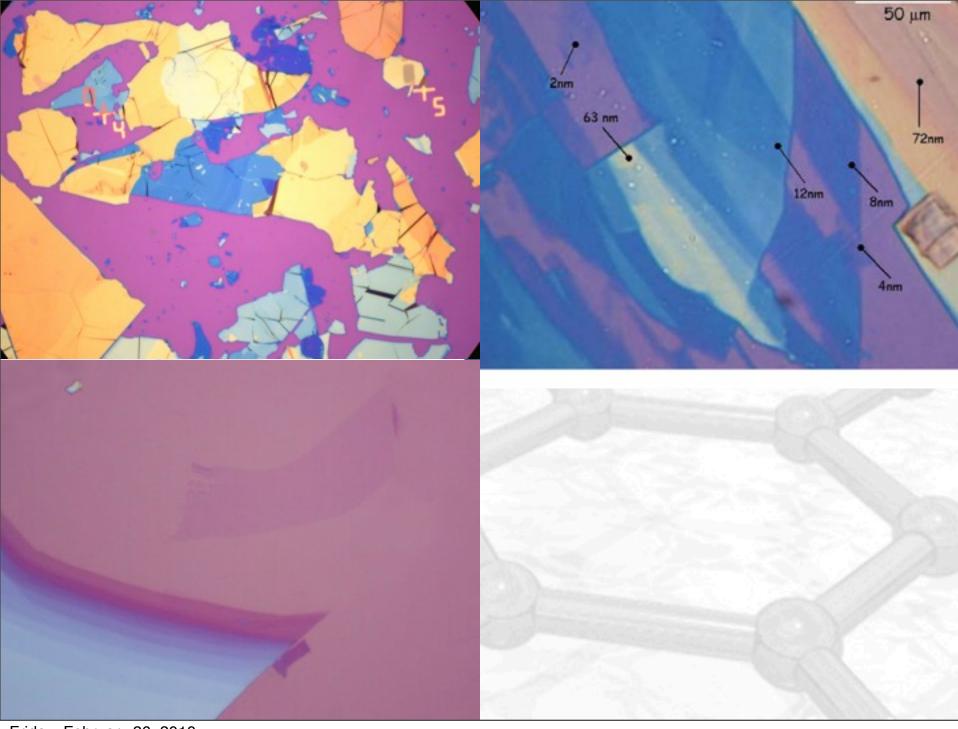
Removing the Scotch Tape



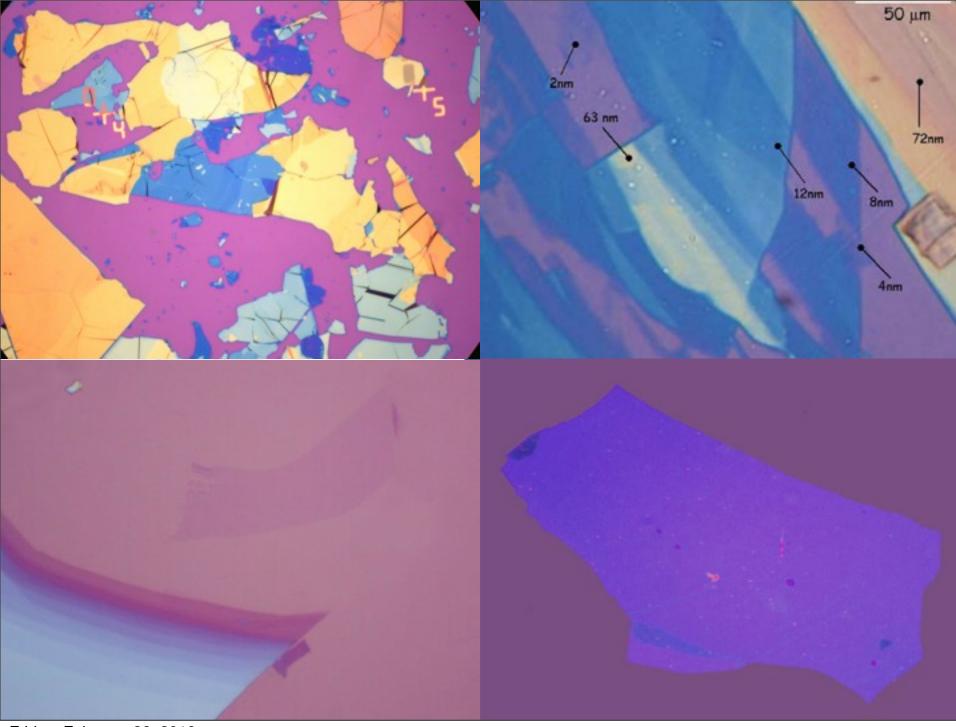
Friday, February 26, 2010



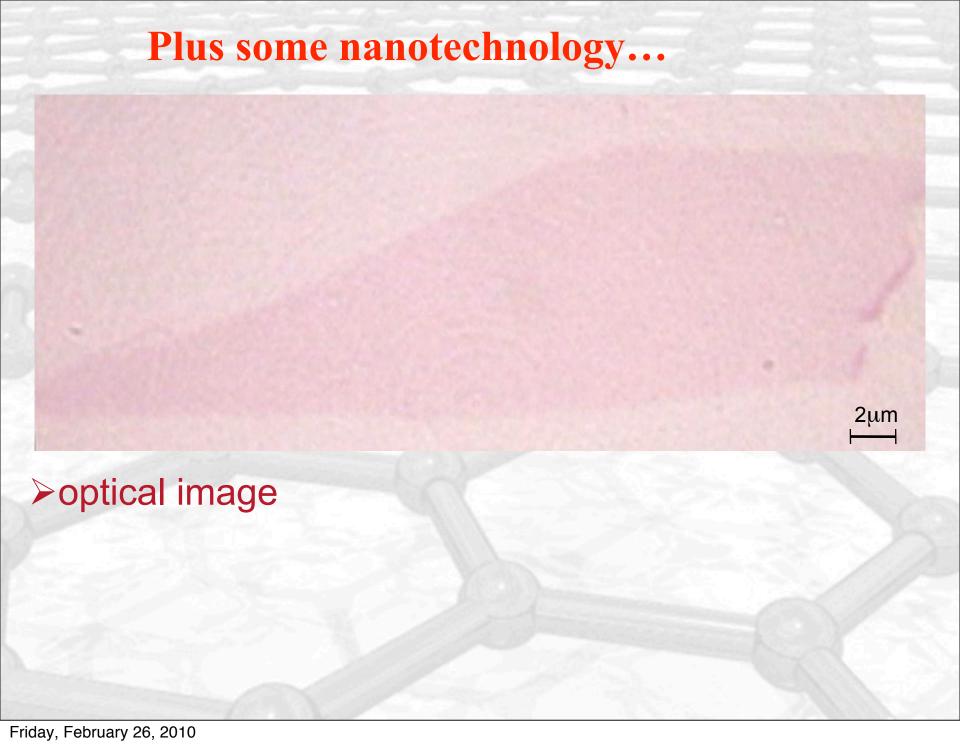
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Friday, February 26, 2010



Friday, February 26, 2010

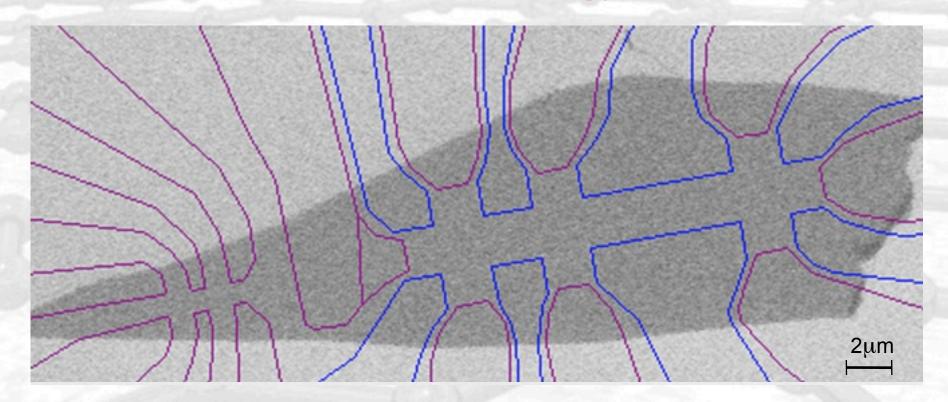


Plus some nanotechnology...

≥ optical image

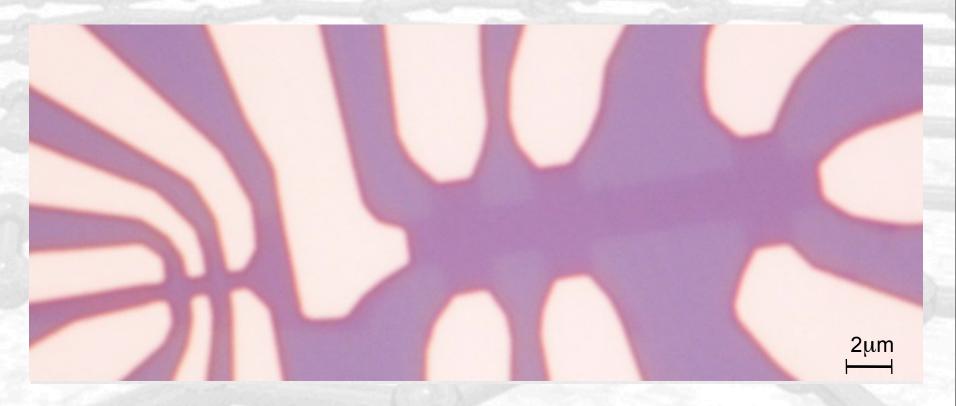
➤ SEM image

Plus some nanotechnology...

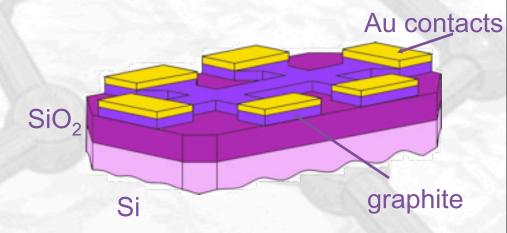


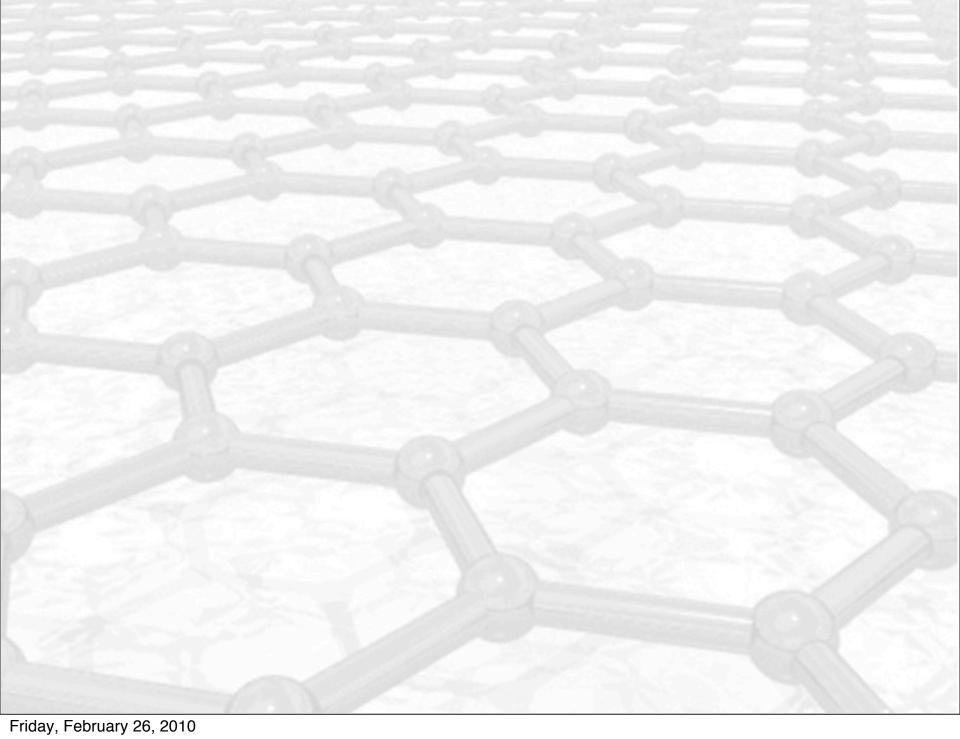
- ➤optical image
- ➤ SEM image
- ➤ design

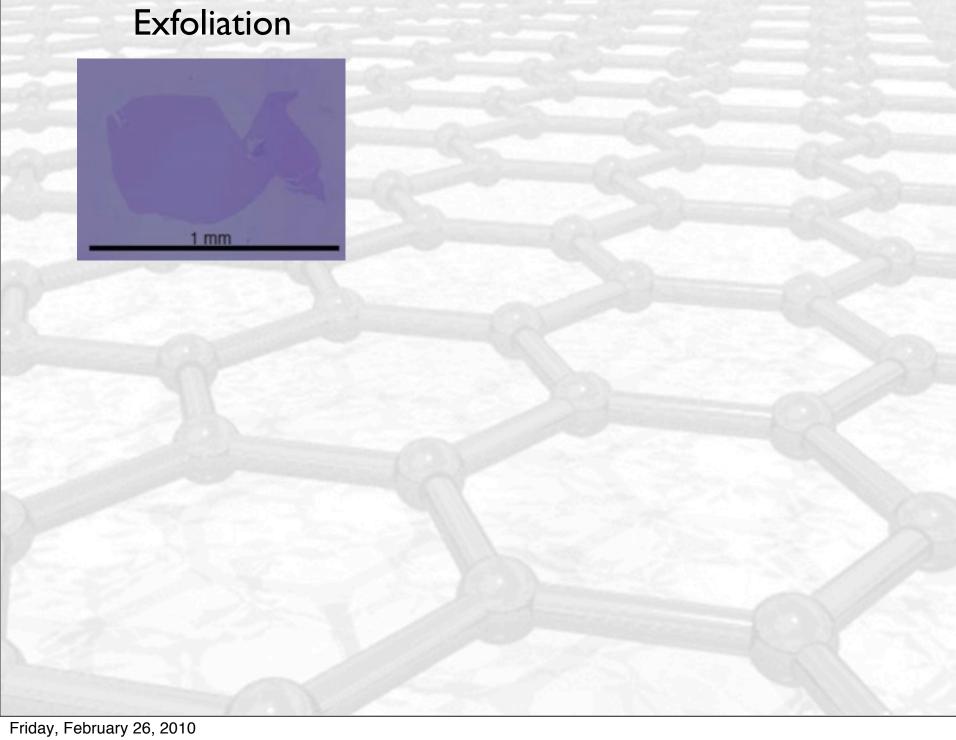
Plus some nanotechnology...



- ➤optical image
- >SEM image
- ▶ design
- >contacts and mesa

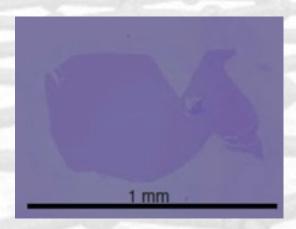




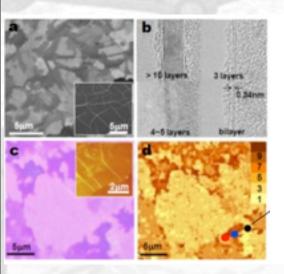


Growth on SiC Exfoliation 1 mm Berger et al., J. Phys. Chem. B, 2004, 108 (52)

Exfoliation

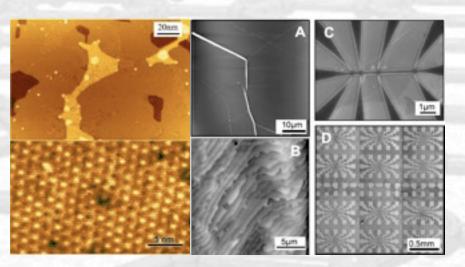


Growth by CVD



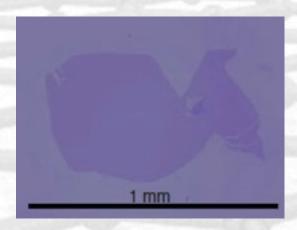
Kim et al., Nature 457, 706-710 (2009)

Growth on SiC



Berger et al., J. Phys. Chem. B, 2004, 108 (52)

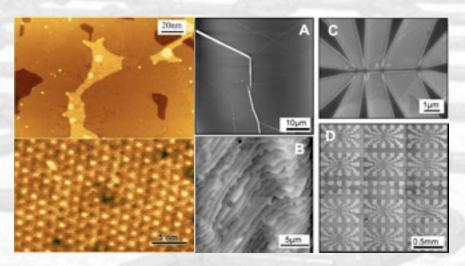
Exfoliation



Growth by CVD

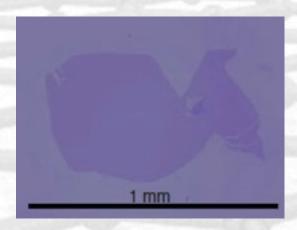


Growth on SiC



Berger et al., J. Phys. Chem. B, 2004, 108 (52)

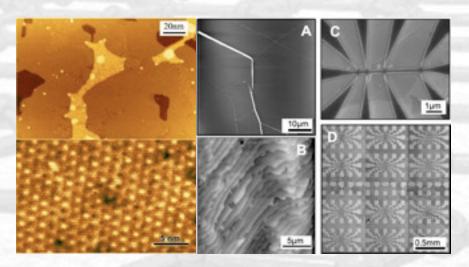
Exfoliation



Growth by CVD

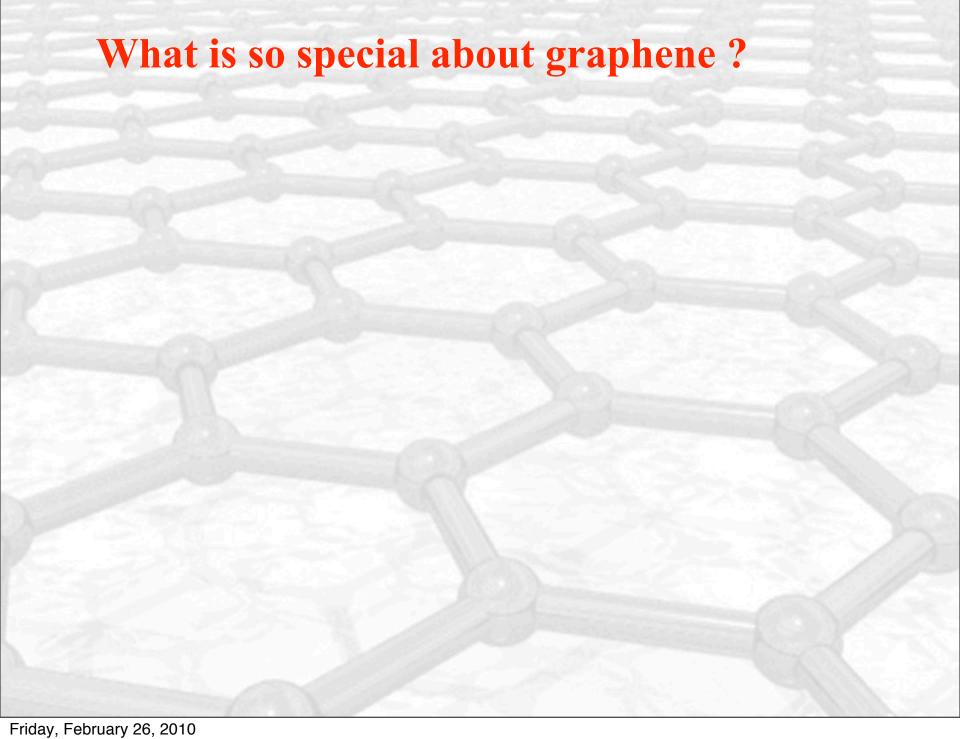


Growth on SiC

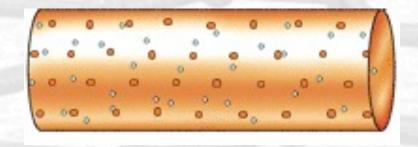


Berger et al., J. Phys. Chem. B, 2004, 108 (52)

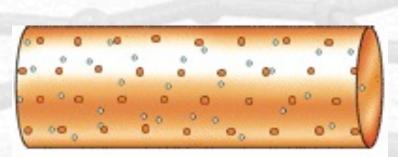




Normal conductor

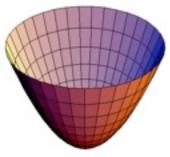


Normal conductor Fermions



$$E(p) = \frac{p^2}{2m}$$

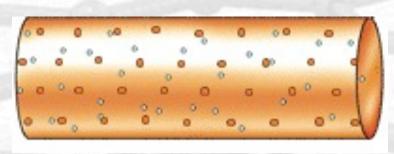




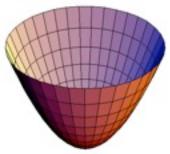
Normal conductor

Fermions

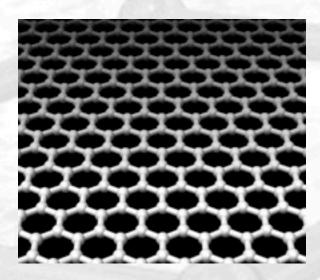




$$E(p) = \frac{p^2}{2m}$$



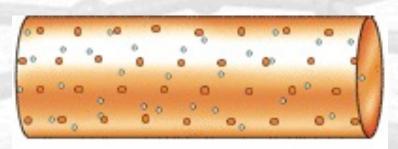
Graphene



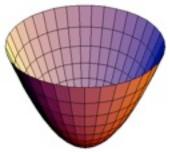
Normal conductor

Fermions

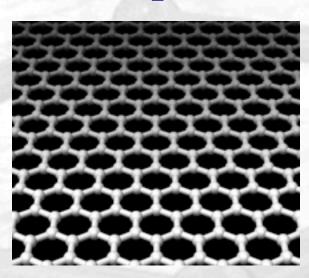




$$E(p) = \frac{p^2}{2m}$$

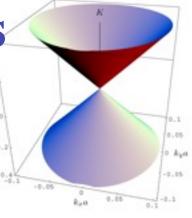








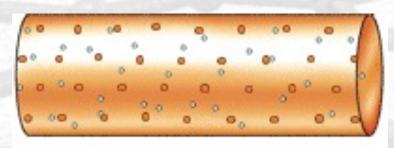
$$E(p) = \pm v p_{\text{e}(v)}$$



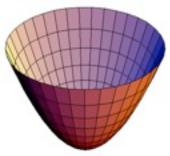
Normal conductor

Fermions

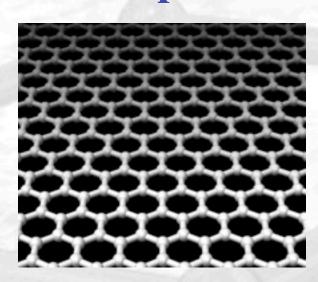




$$E(p) = \frac{p^2}{2m}$$



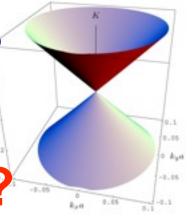
Graphene





$$E(p) = \pm v p$$

But how???



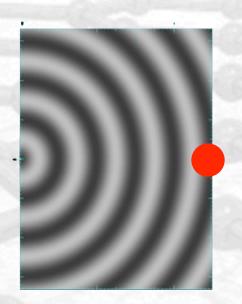
Wave-particle duality

particle

Wave-particle duality

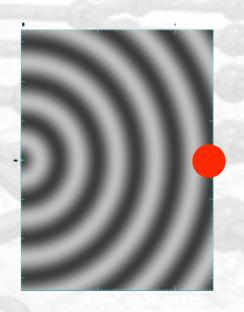
particle

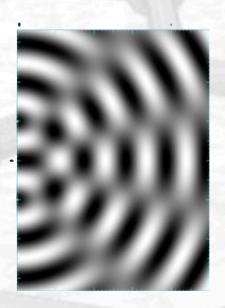
Wave-particle duality



particle ← → wave

Wave-particle duality

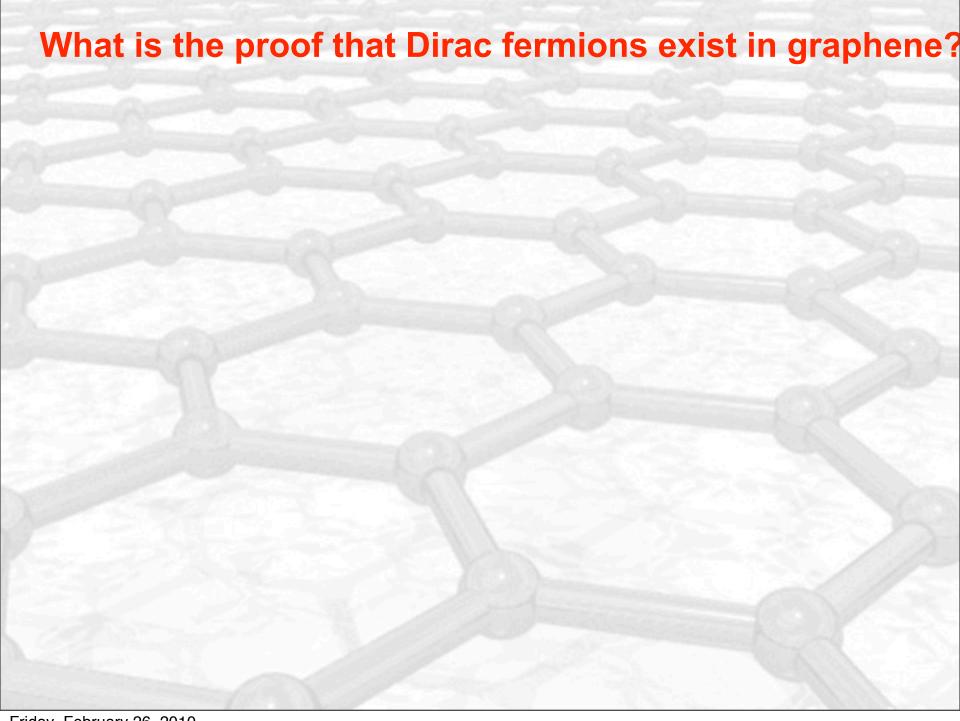




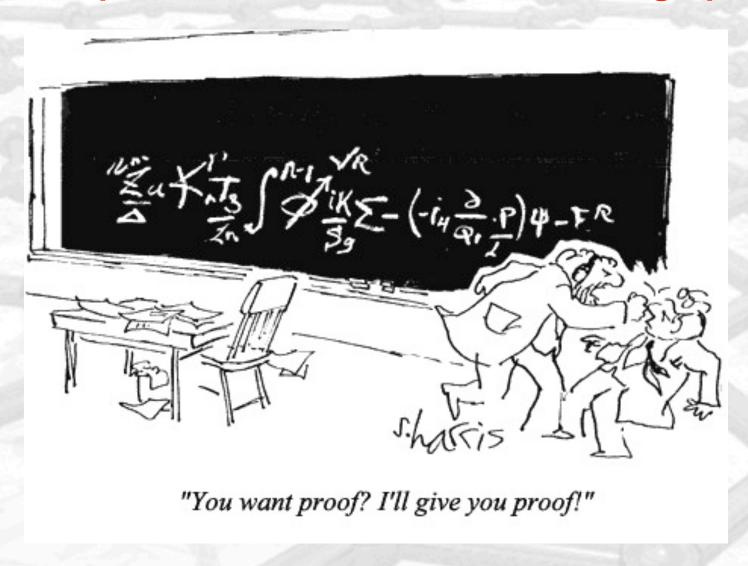
particle ← wave

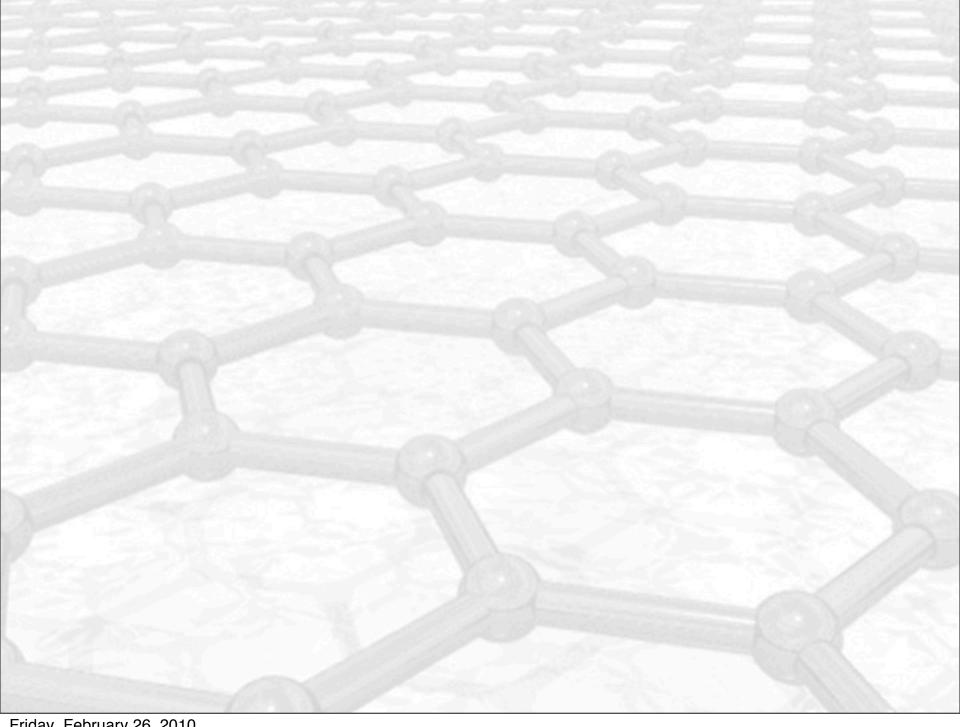
Interference

Dirac fermions are the final result!



What is the proof that Dirac fermions exist in graphene?





Friday, February 26, 2010

LETTERS

Two-dimensional gas of massless Dirac fermions in graphene

K. S. Novoselov¹, A. K. Geim¹, S. V. Morozov², D. Jiang¹, M. I. Katsnelson³, I. V. Grigorieva¹, S. V. Dubonos² & A. A. Firsov²

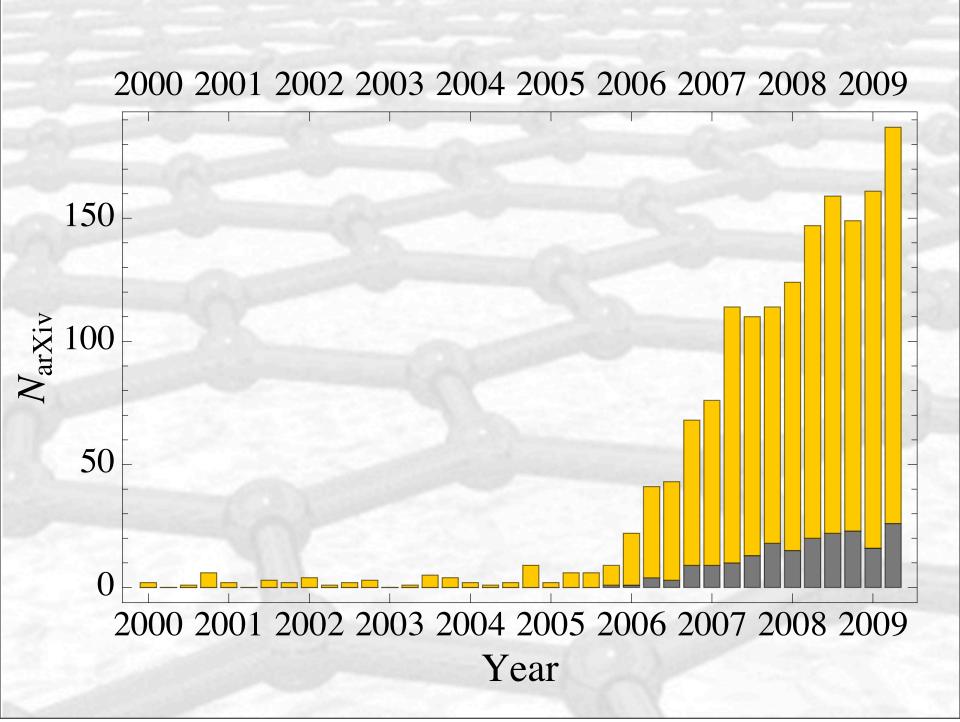
Vol 438|10 November 2005|doi:10.1038/nature04235

nature

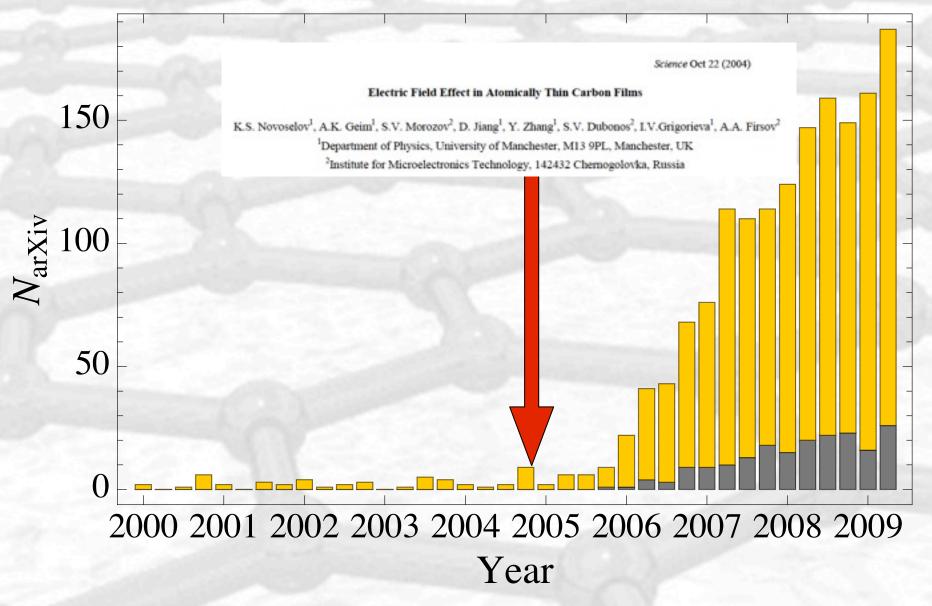
LETTERS

Experimental observation of the quantum Hall effect and Berry's phase in graphene

Yuanbo Zhang¹, Yan-Wen Tan¹, Horst L. Stormer^{1,2} & Philip Kim¹



2000 2001 2002 2003 2004 2005 2006 2007 2008 2009



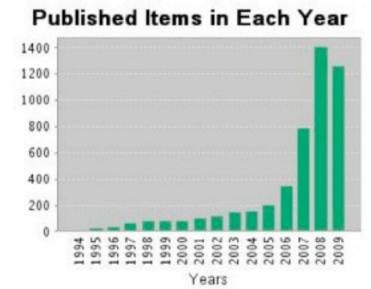
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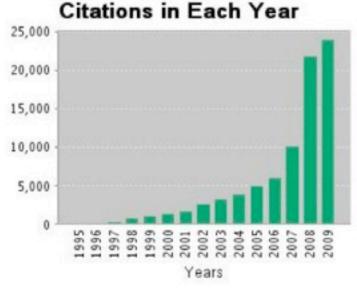
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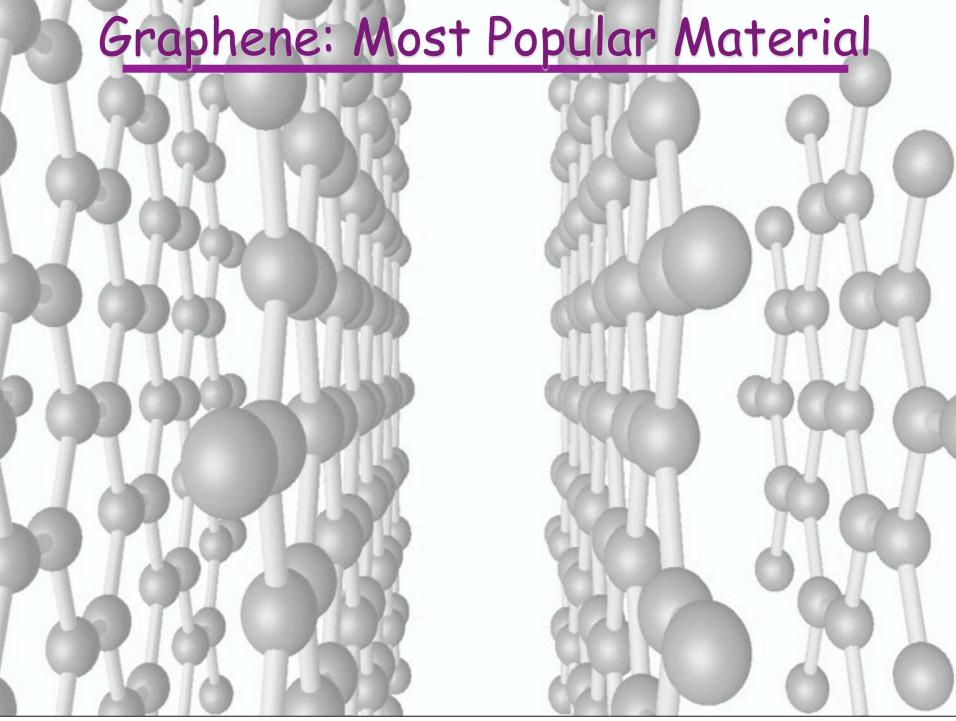
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h-index [?]: 114



rank search word frequency

searches on all Nature websites during 2009

frequency rank search word obesity

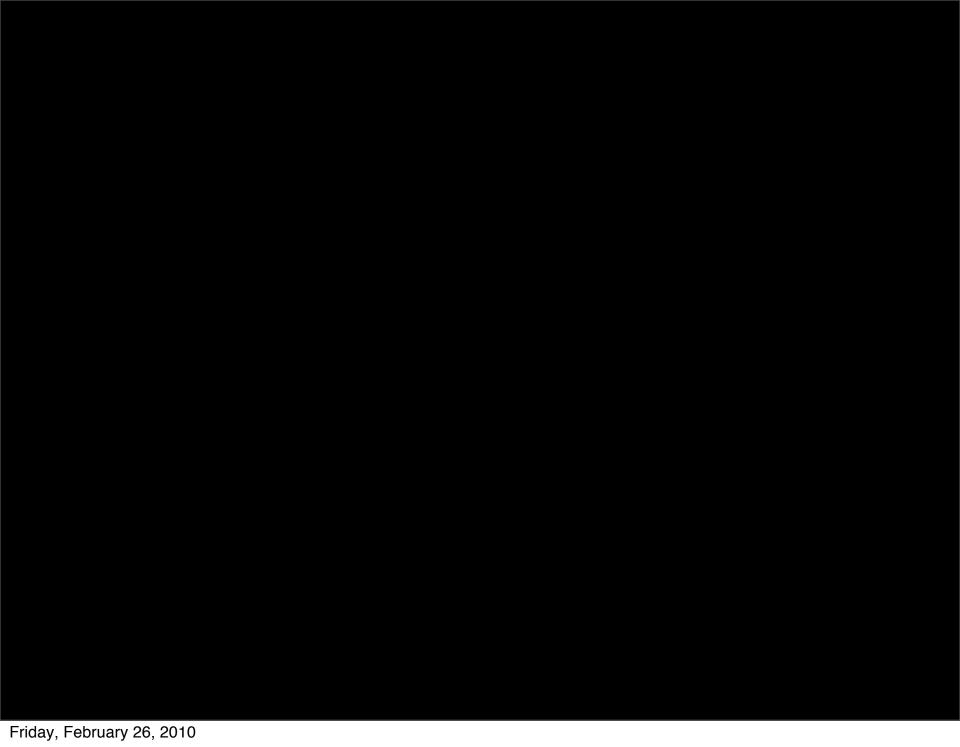
searches on all Nature websites during 2009

rank	search word	frequency
2	cancer	~2.0
3	HIV	1.3
4	apoptosis	1.03
5	obesity	1.0

searches on all Nature websites during 2009

rank	search word	frequency
33.4	graphene	~3.0
2	cancer	~2.0
3	HIV	1.3
74	apoptosis	1.03
5	obesity	1.0

searches on all Nature websites during 2009



The Big-Bang Theory Episode: "Einstein's Approximation"

The electronic properties of graphene

A. H. Castro Neto

Department of Physics, Boston University, 590 Commonwealth Avenue, Boston, Massachusetts 02215, USA

F. Guinea

Instituto de Ciencia de Materiales de Madrid, CSIC, Cantoblanco, E-28049 Madrid, Spain

N. M. R. Peres

Center of Physics and Department of Physics, Universidade do Minho, P-4710-057, Braga, Portugal

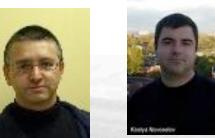
K. S. Novoselov and A. K. Geim

Department of Physics and Astronomy, University of Manchester, Manchester, M13 9PL, United Kingdom

(Published 14 January 2009)



Paco Guinea Nuno Peres



Kostya Novoselov



Andre Geim

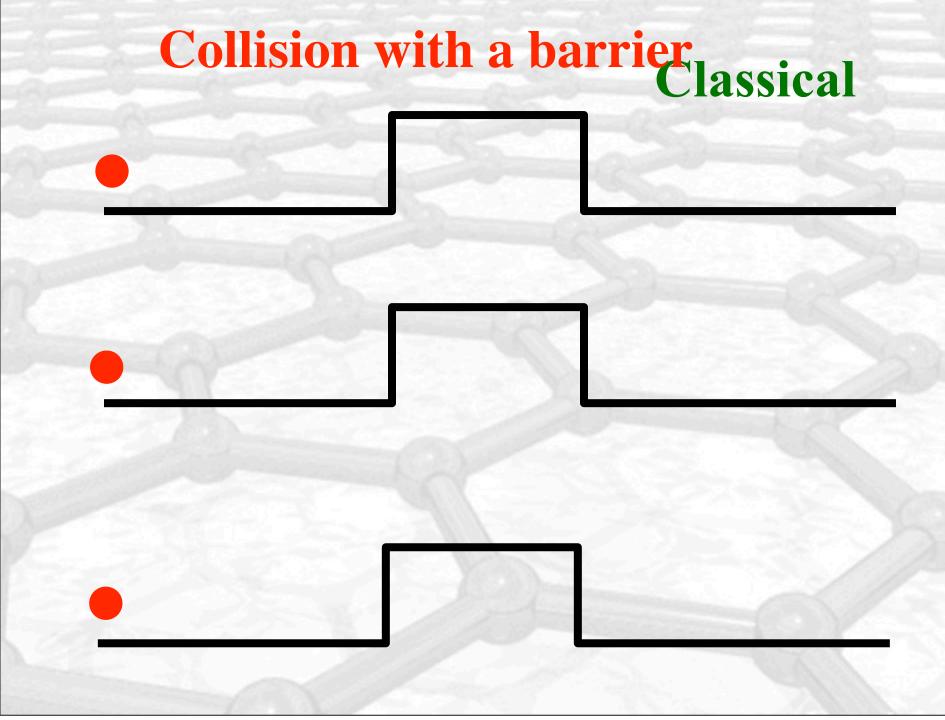
$$E(p) = \pm v p$$

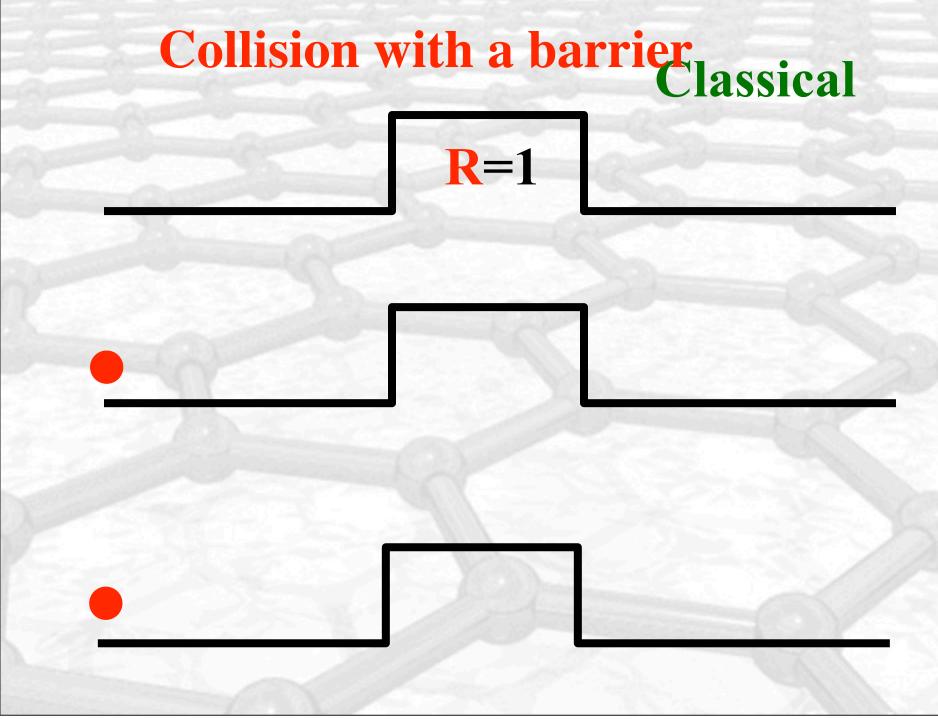
Electrons propagate just as light does.

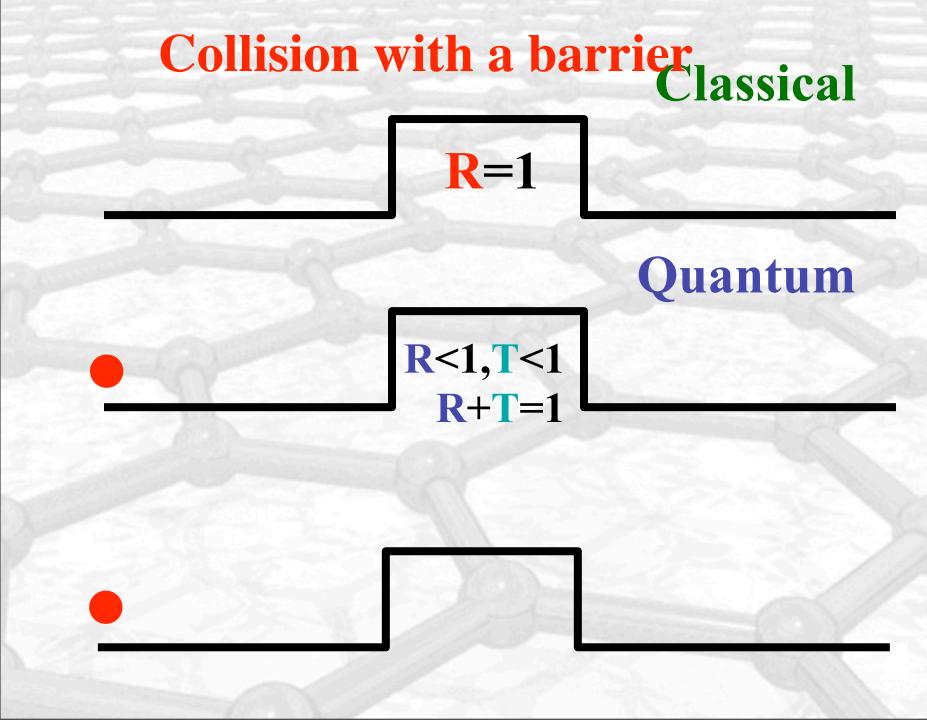
$$v = c/300$$

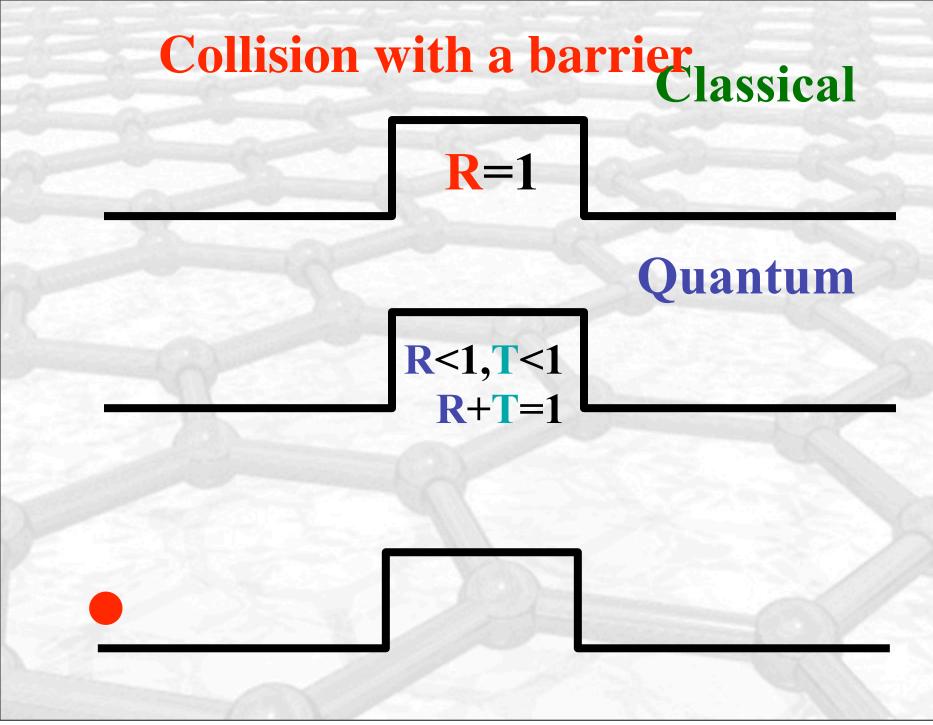
Relativity at very low speed of light"

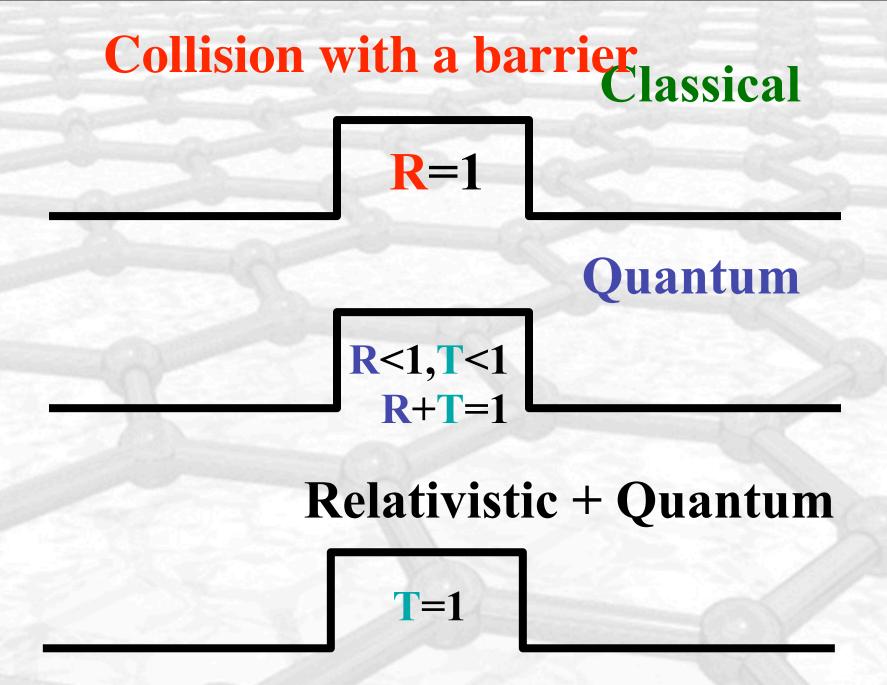
Weirdness of Quantum Physics plus Relativity!

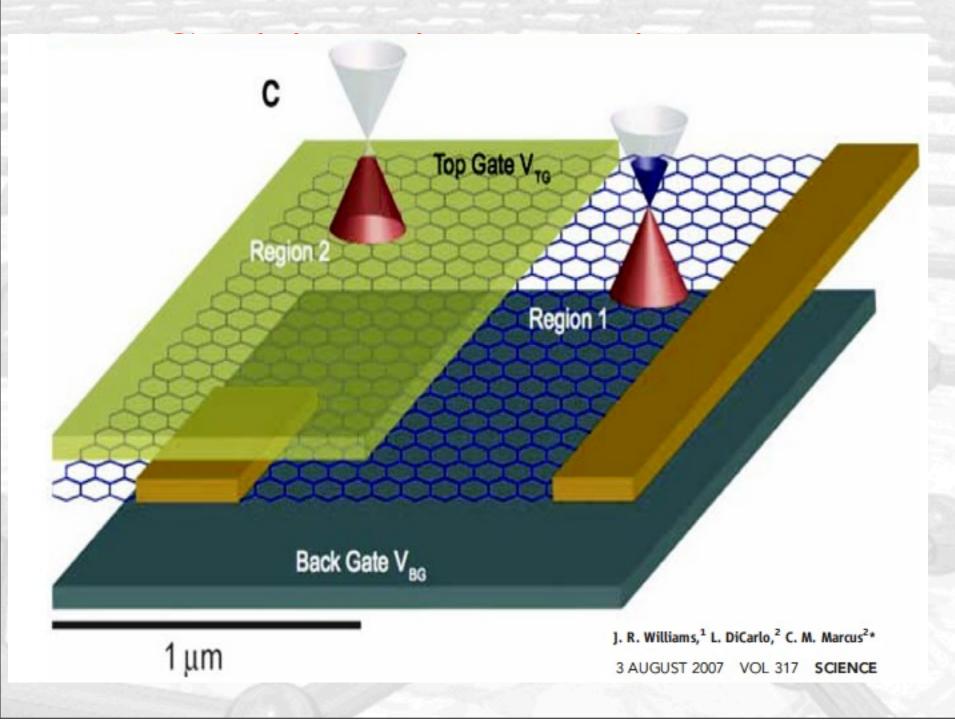


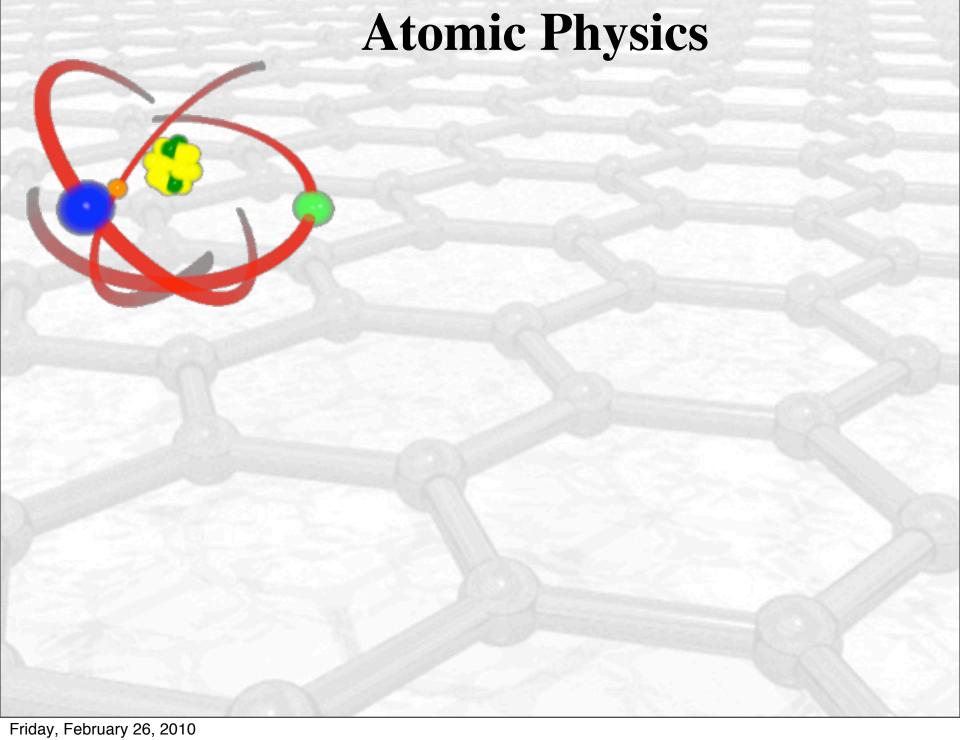


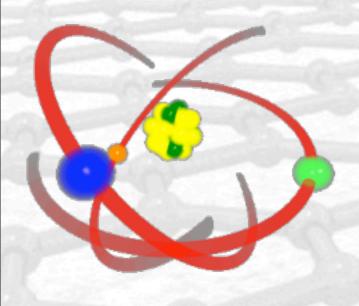




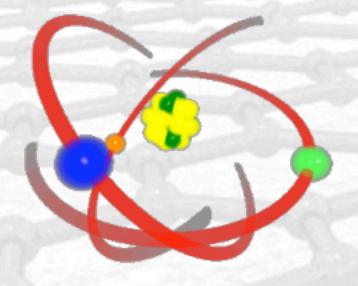




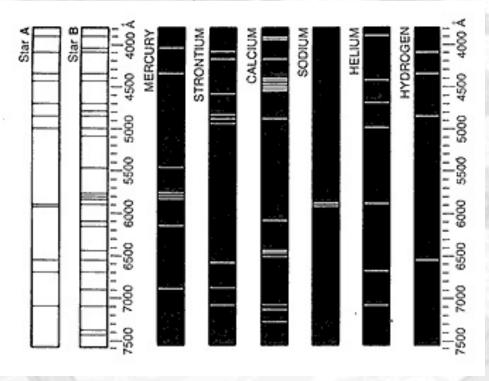


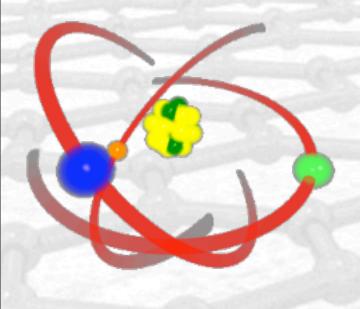


$$V(r) = -Z \frac{e^2}{\varepsilon_0} \frac{1}{r}$$
 Coulomb law

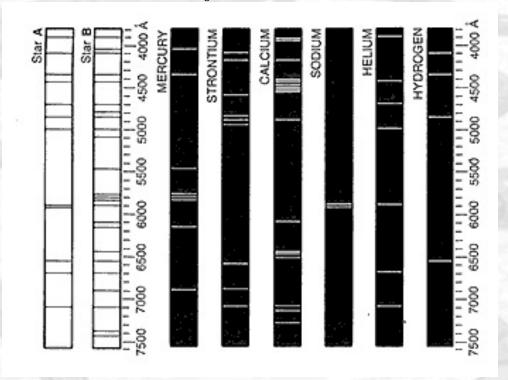


$$V(r) = -Z \frac{e^2}{\varepsilon_0} \frac{1}{r}$$
 Coulomb law



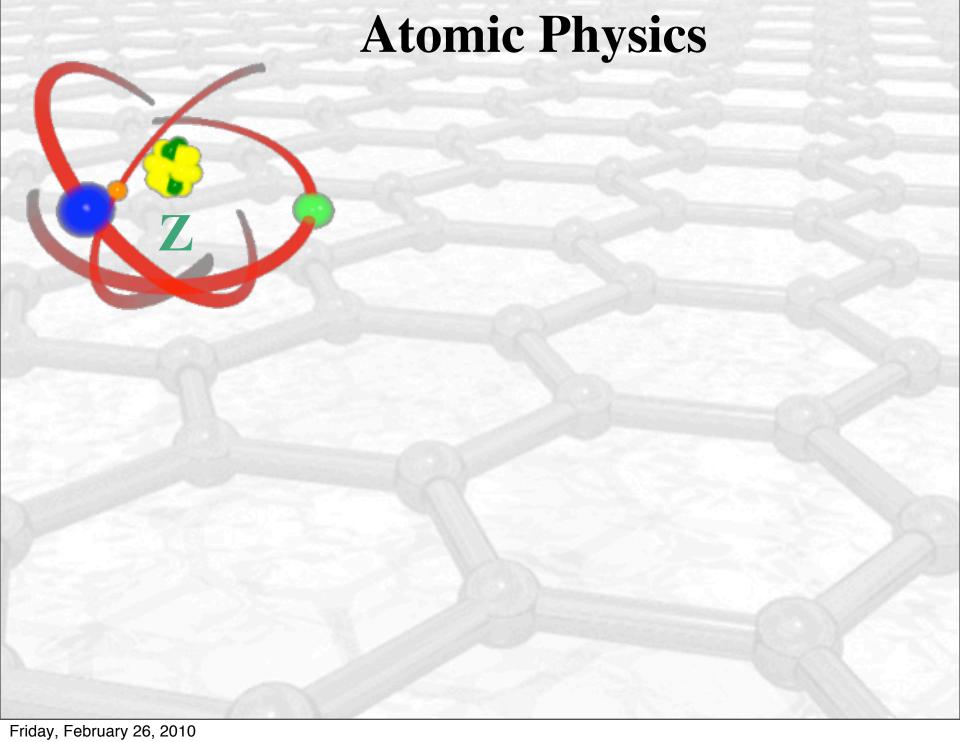


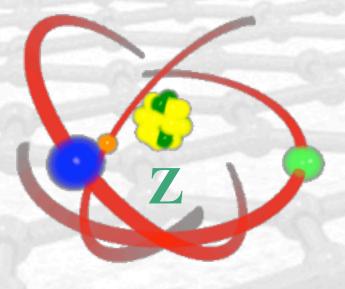
$$V(r) = -Z \frac{e^2}{\varepsilon_0} \frac{1}{r}$$
 Coulomb law



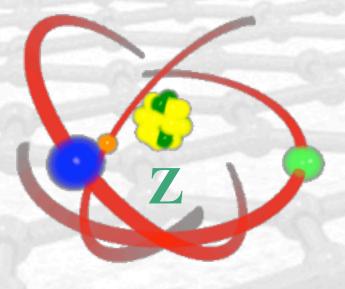
Fine structure constant

$$\alpha = \frac{e^2}{\epsilon_0 hc} = 0.007297352536(5) \approx \frac{1}{137}$$

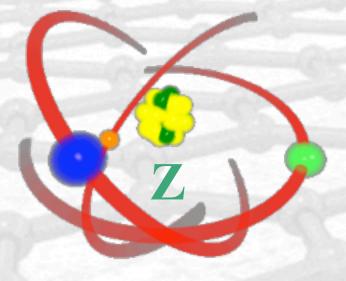




$$Z < \frac{1}{\alpha} \approx 137$$



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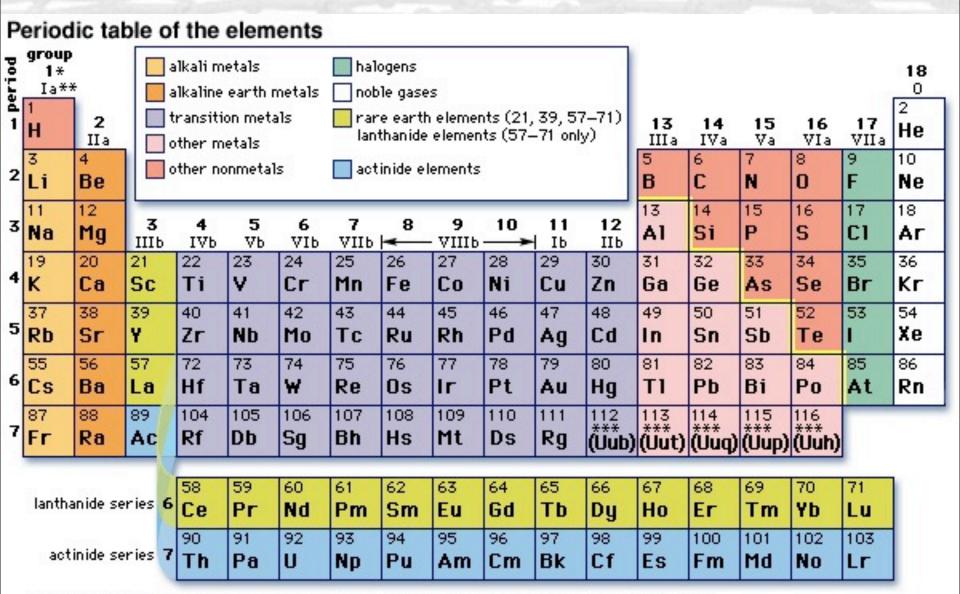


$$Z < \frac{1}{\alpha} \approx 137$$

$$Z > \frac{1}{\alpha} \approx 137$$
 Overcritical Atom



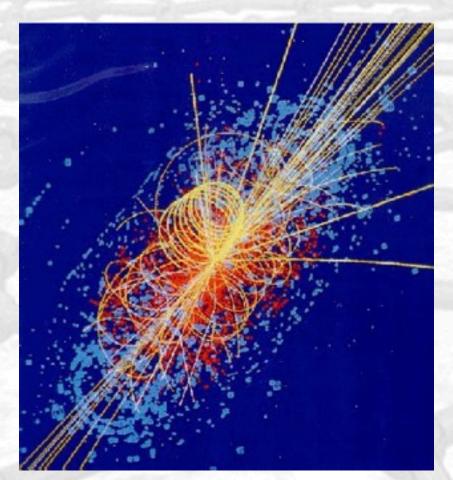
Positron emission

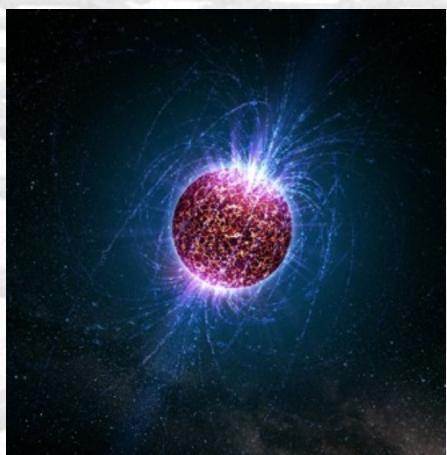


^{*}Numbering system adopted by the International Union of Pure and Applied Chemistry (IUPAC).

^{**} Numbering system widely used, especially in the U.S., from the mid-20th century.

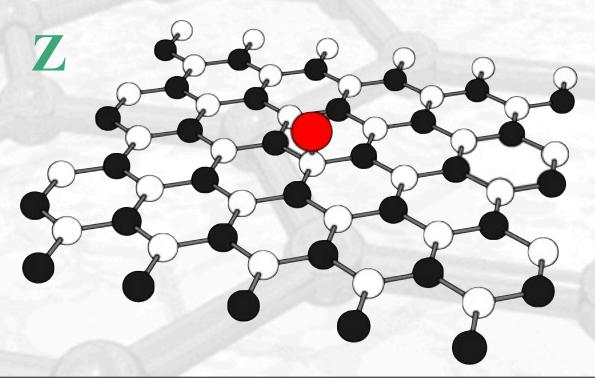
^{***} Discoveries of elements 112—116 are claimed but not confirmed. Element names and symbols in parentheses are temporarily assigned by IUPAC.



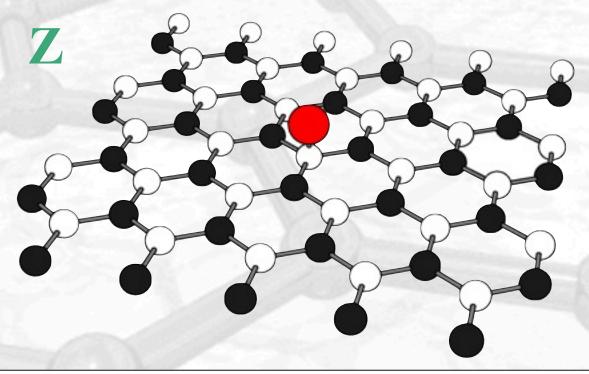


heavy ion collisions

neutron stars



$$\alpha_G = \frac{e^2}{\epsilon_0 h v} \approx 2$$

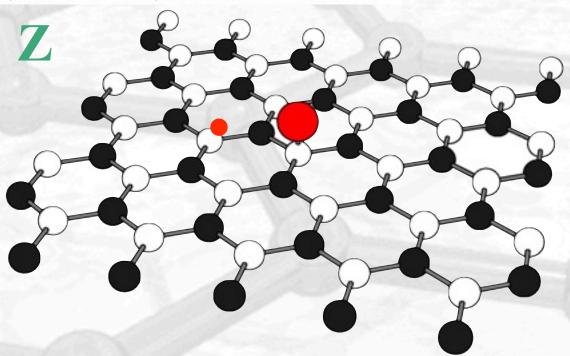


$$\alpha_G = \frac{e^2}{\epsilon_0 h v} \approx 2$$

Atoms become overcritical easily

Coulomb Impurity Problem in Graphene PRL 99, 166802 (2007)

Vitor M. Pereira, Johan Nilsson, and A. H. Castro Neto

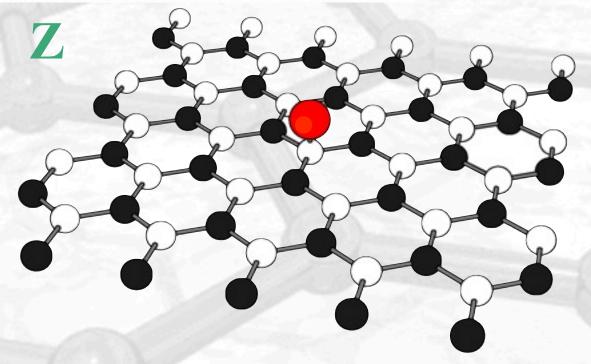


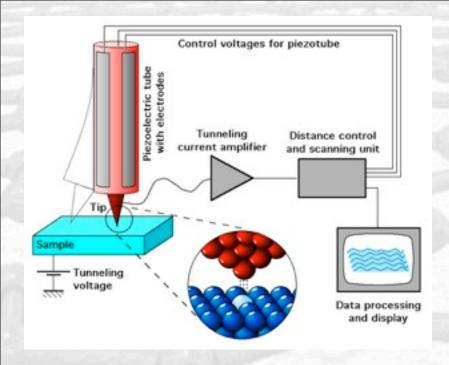
$$\alpha_G = \frac{e^2}{\epsilon_0 h v} \approx 2$$

Atoms become overcritical easily

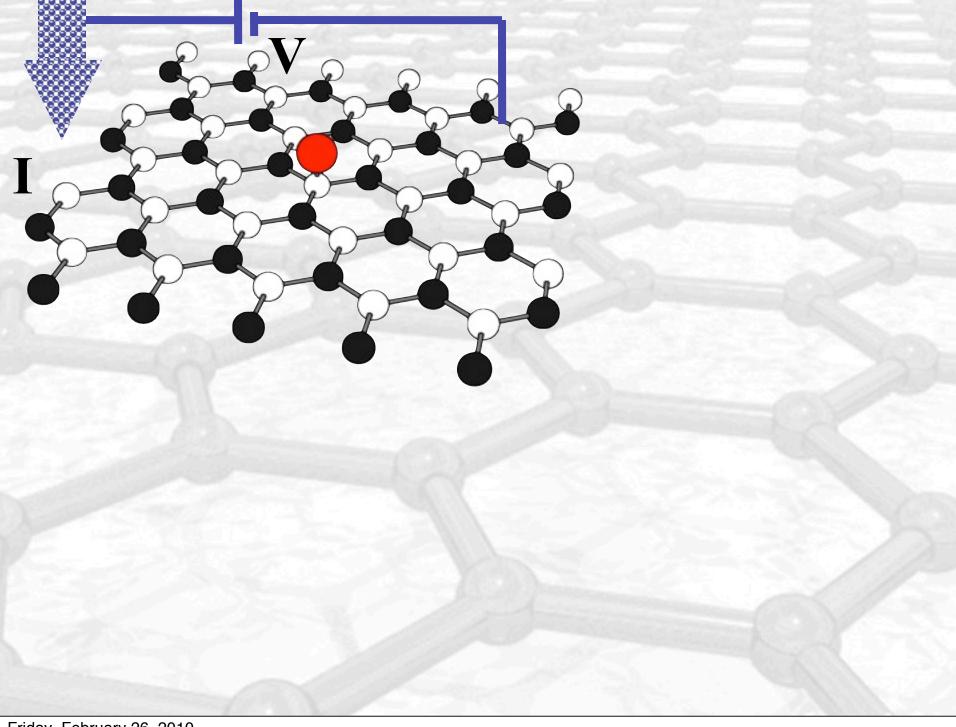
Coulomb Impurity Problem in Graphene PRL 99, 166802 (2007)

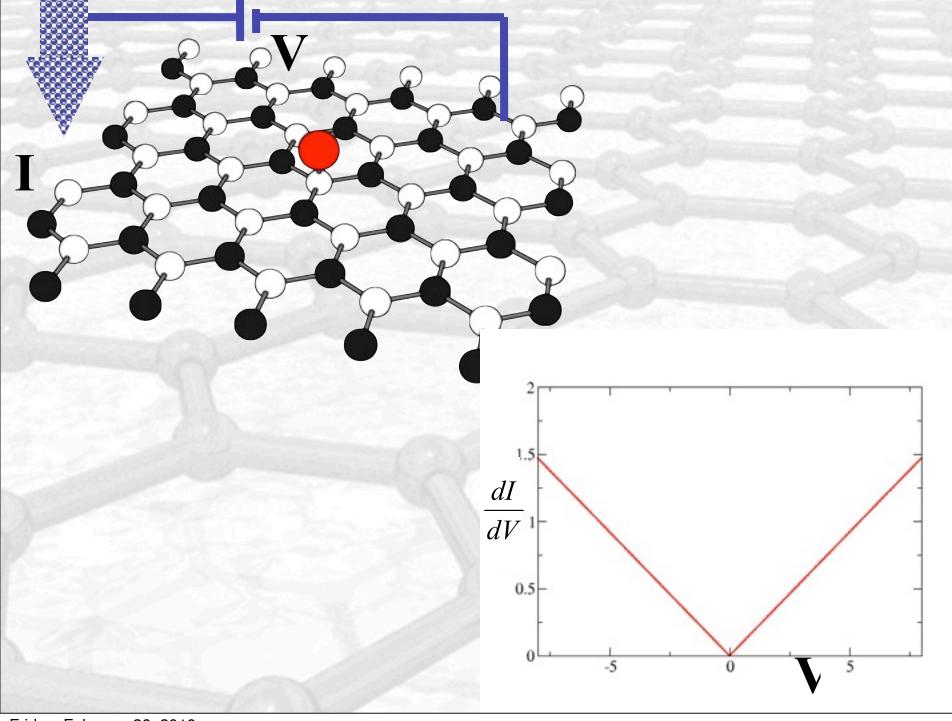
Vitor M. Pereira, Johan Nilsson, and A. H. Castro Neto



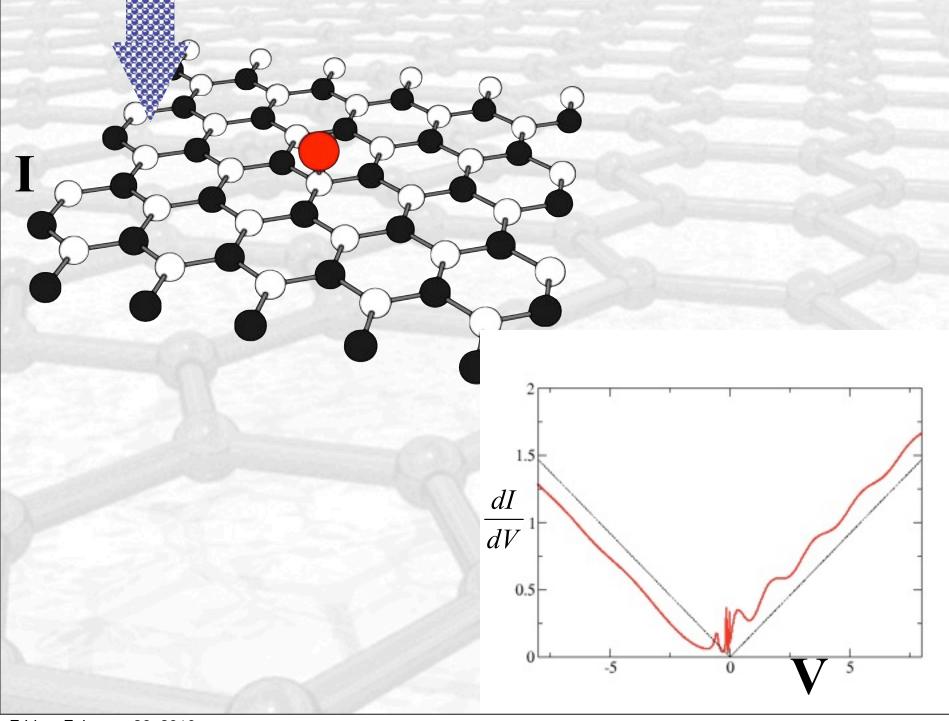


Use a scanning tunneling microscope, for a "high-energy experiment

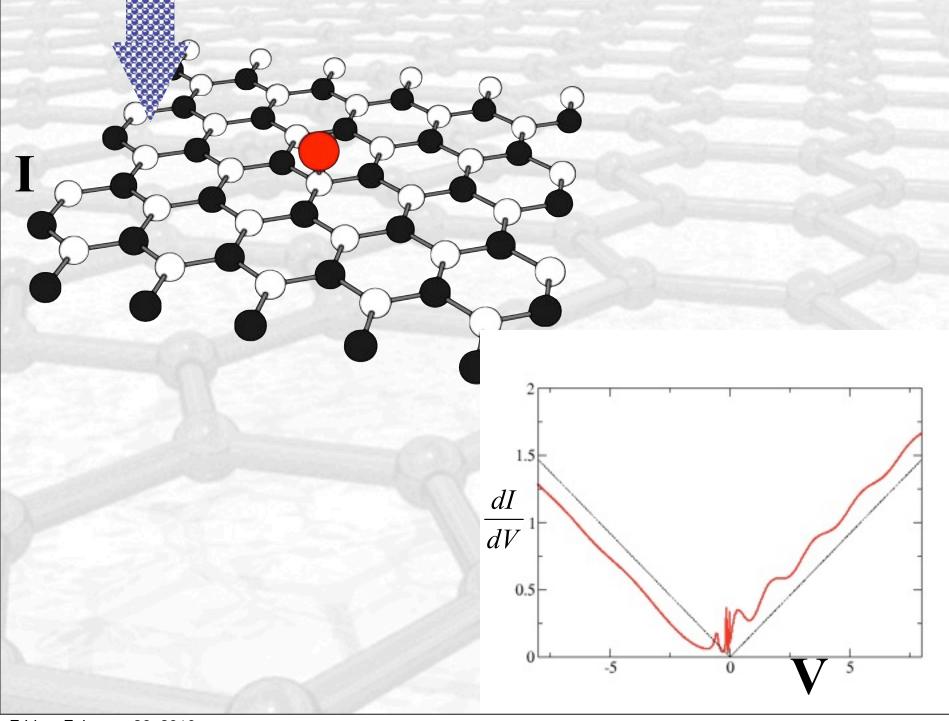




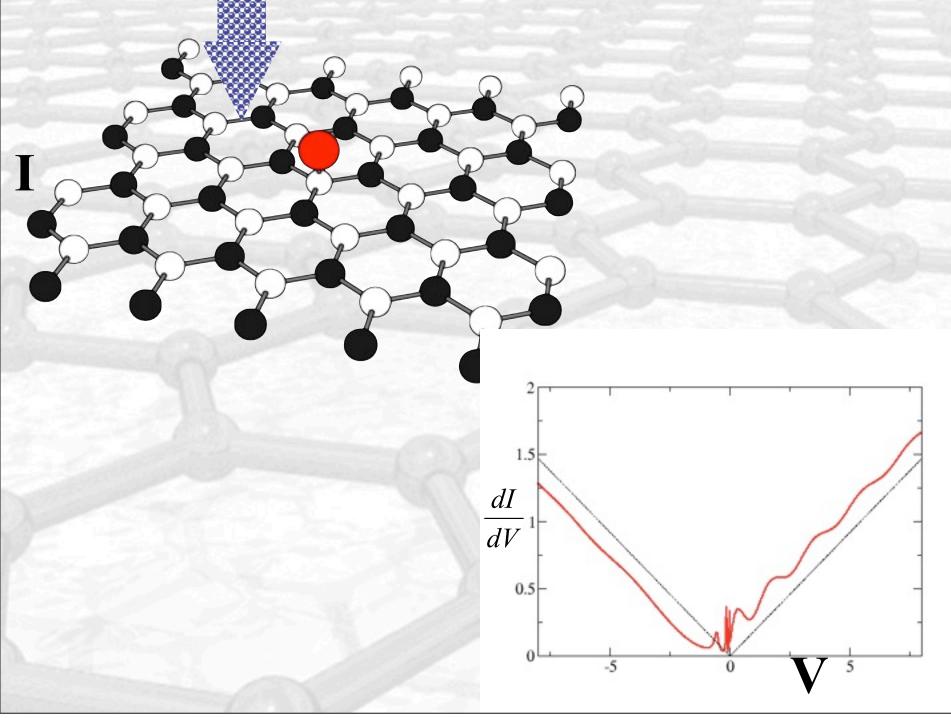
Friday, February 26, 2010



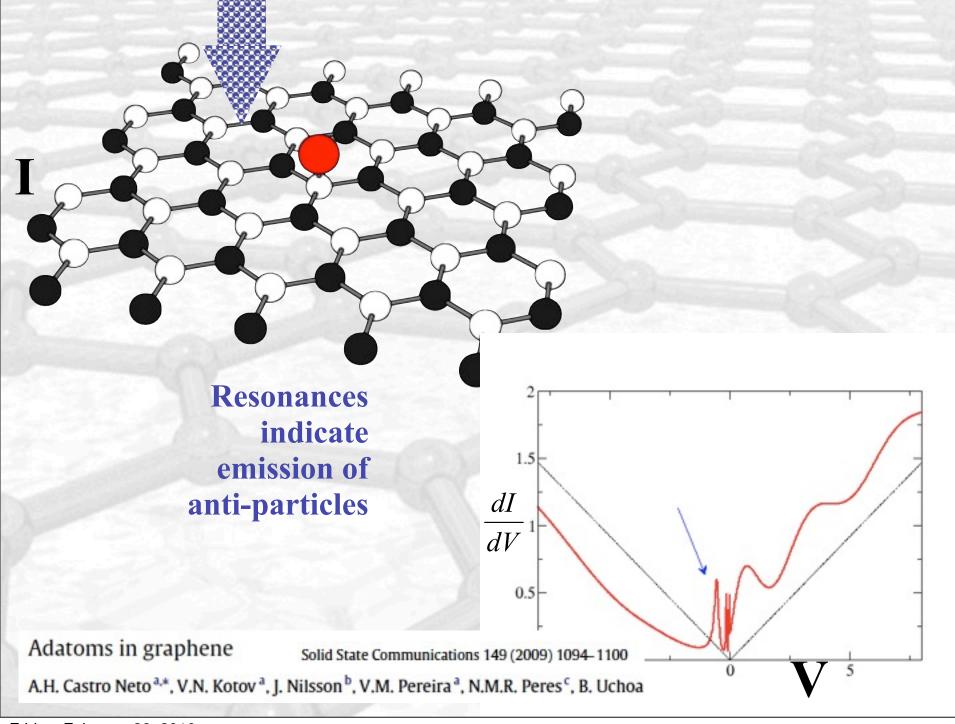
Friday, February 26, 2010

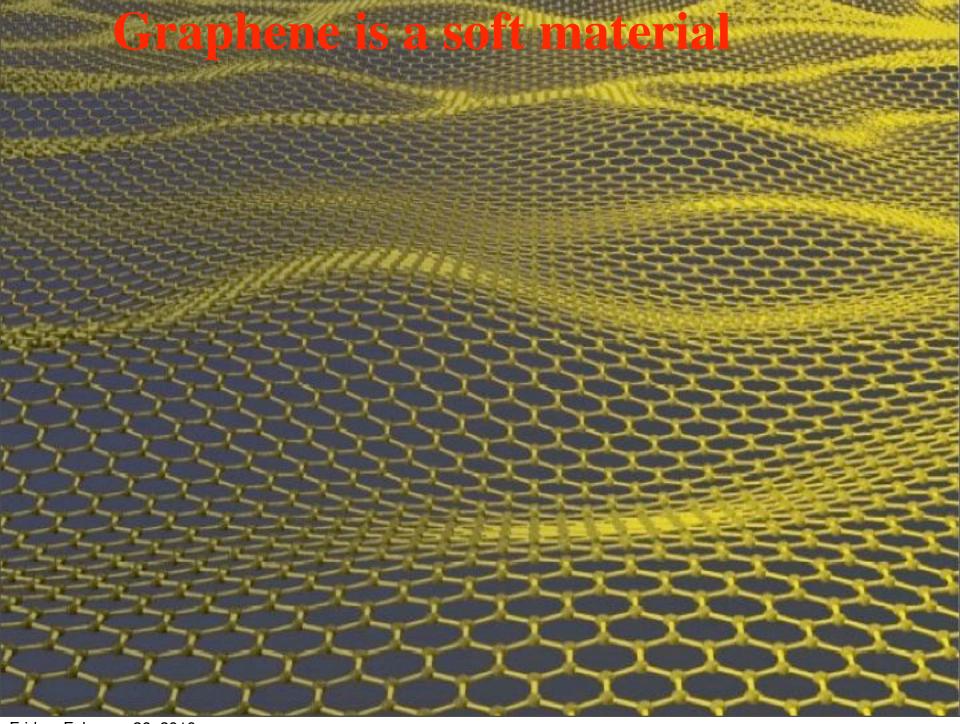


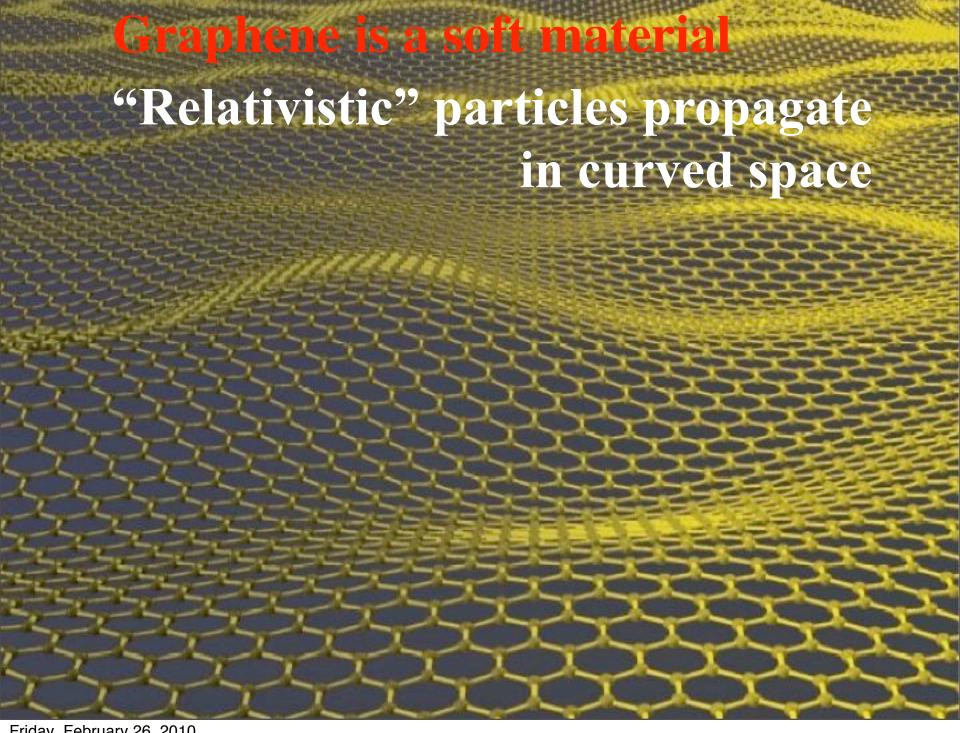
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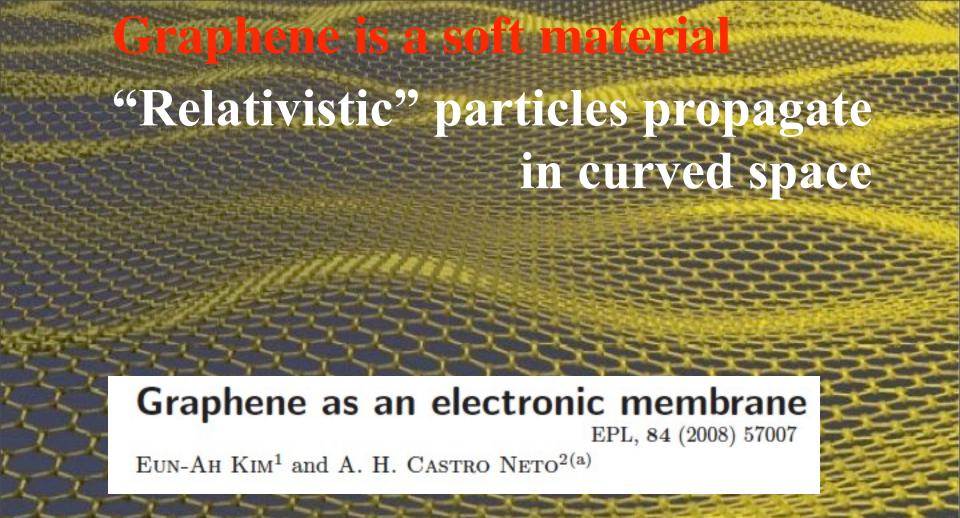


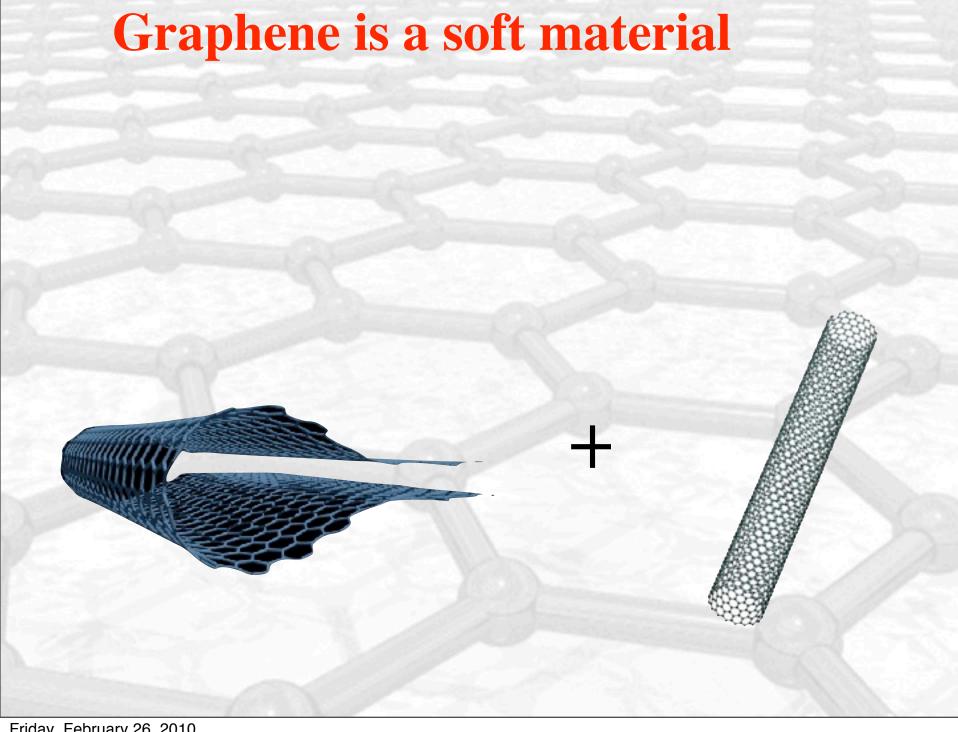
Friday, February 26, 2010

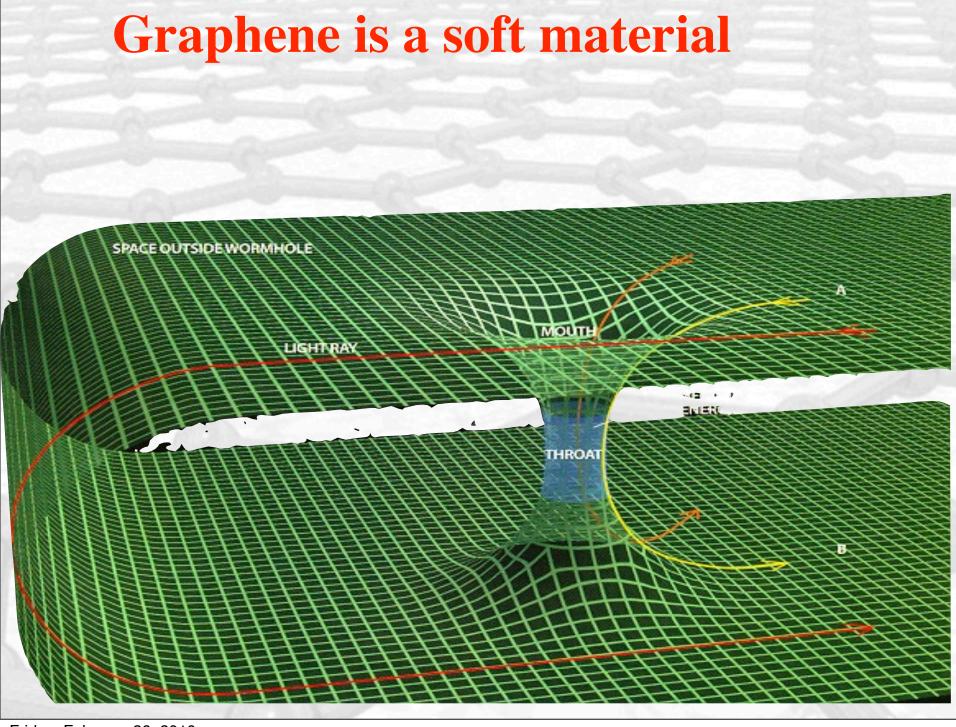














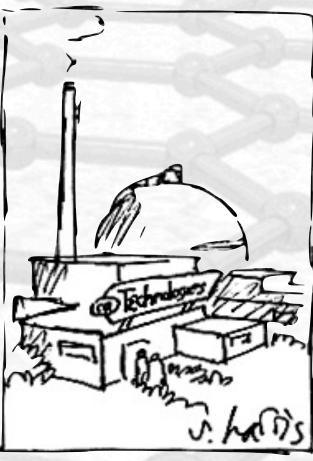
Now ...

Let us go back to Earth

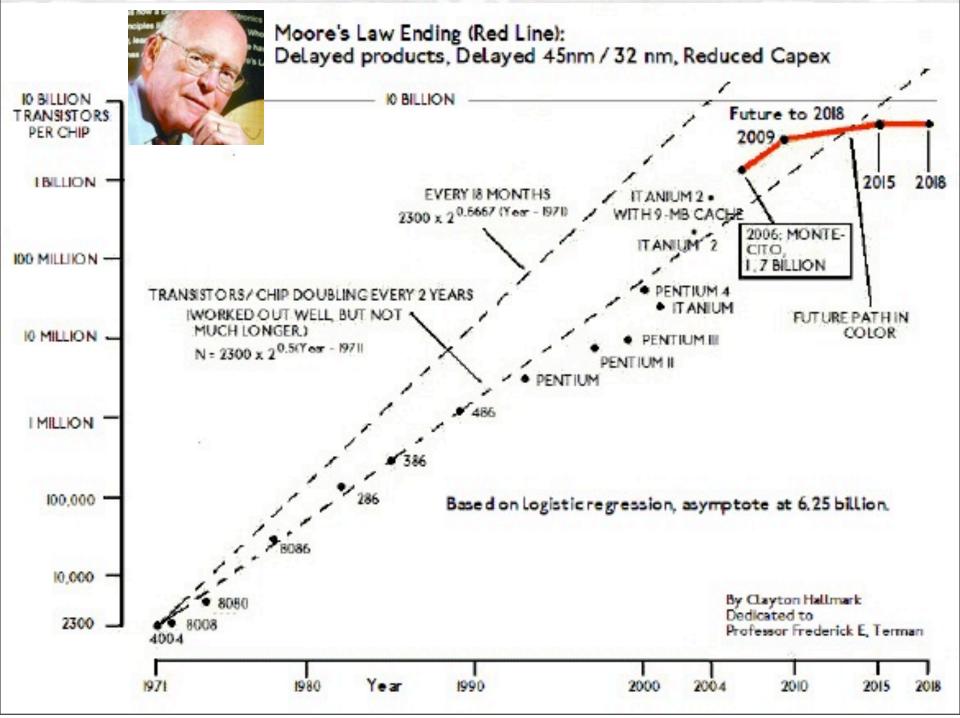
BIG SCIENCE

LITTLE SCIENCE



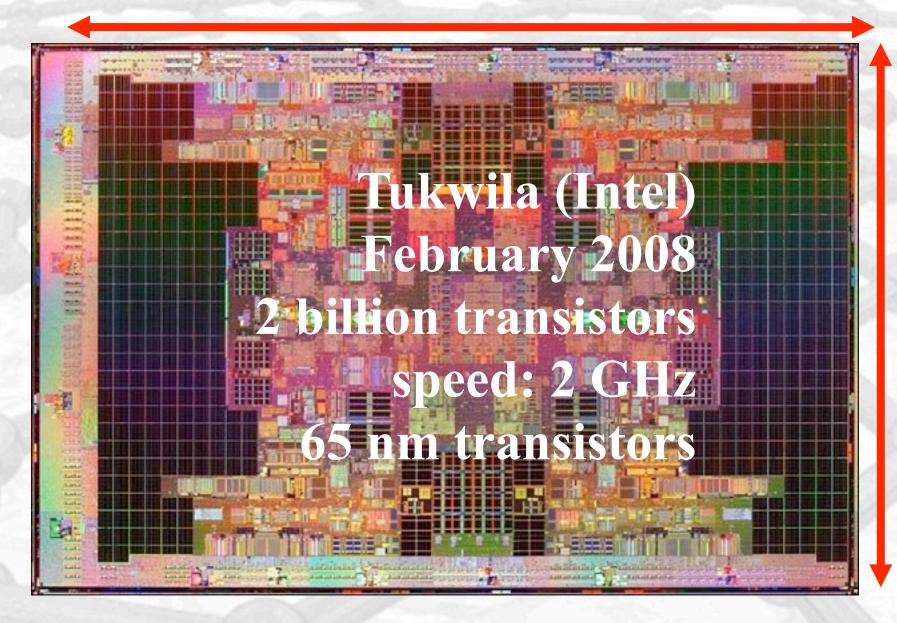


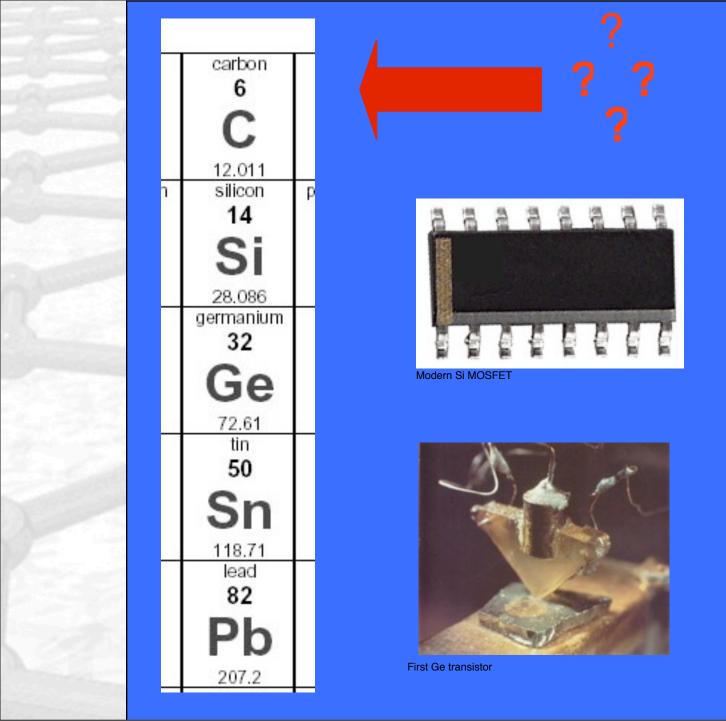
What about applications?

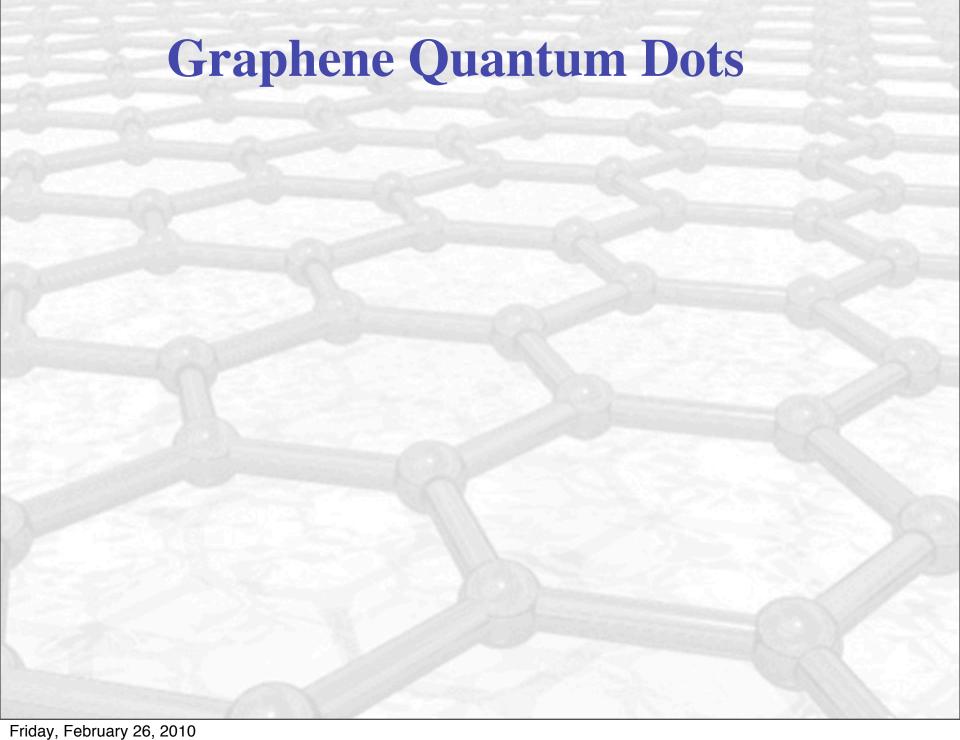


Friday, February 26, 2010

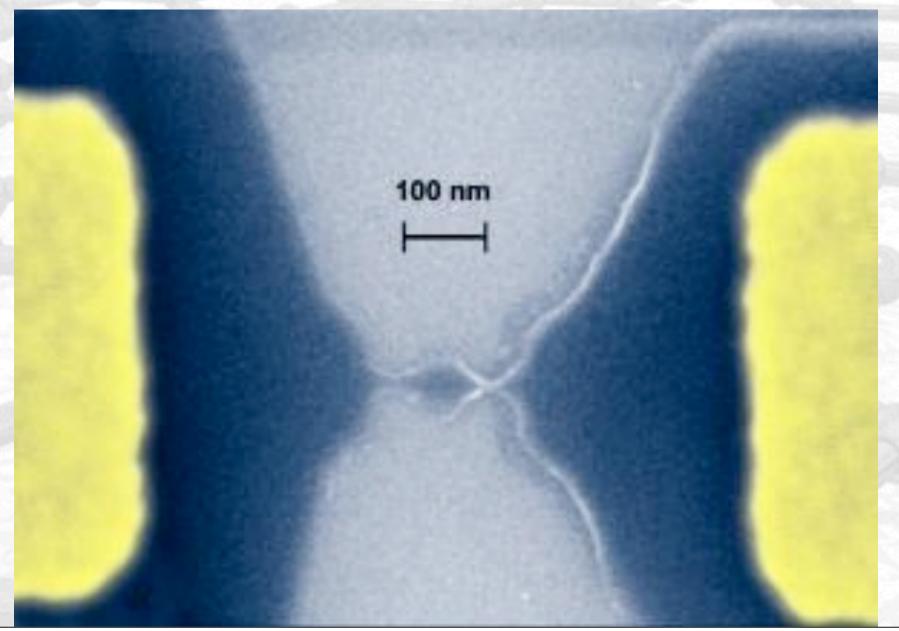
32.5 mm



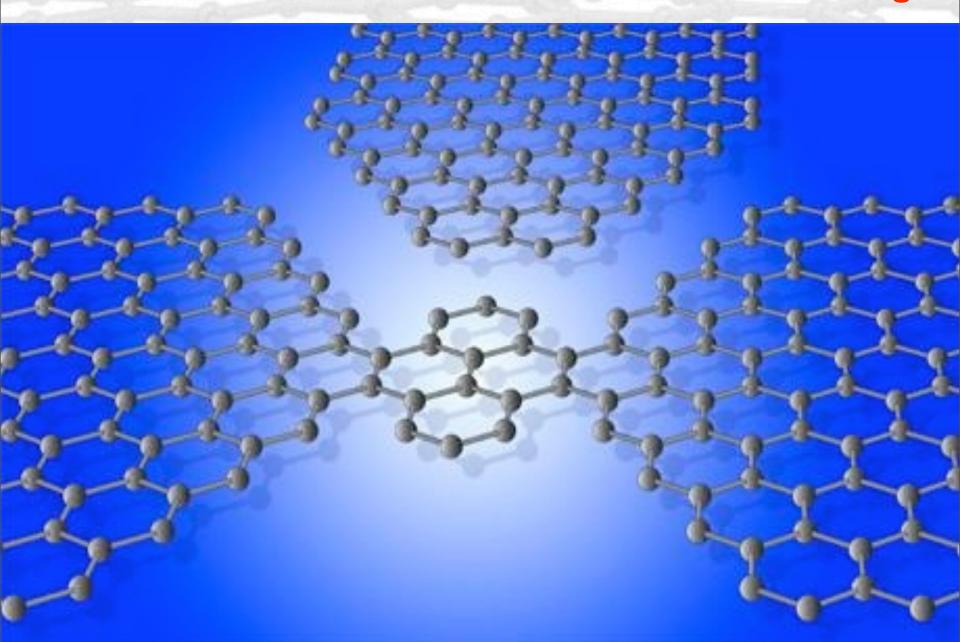




Graphene Quantum Dots



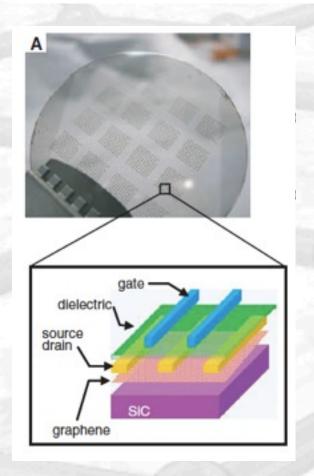
Miniaturization down to 1 nm: a few benzene rings

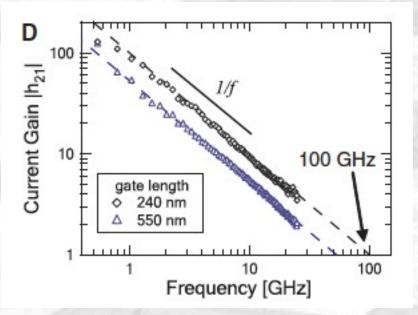


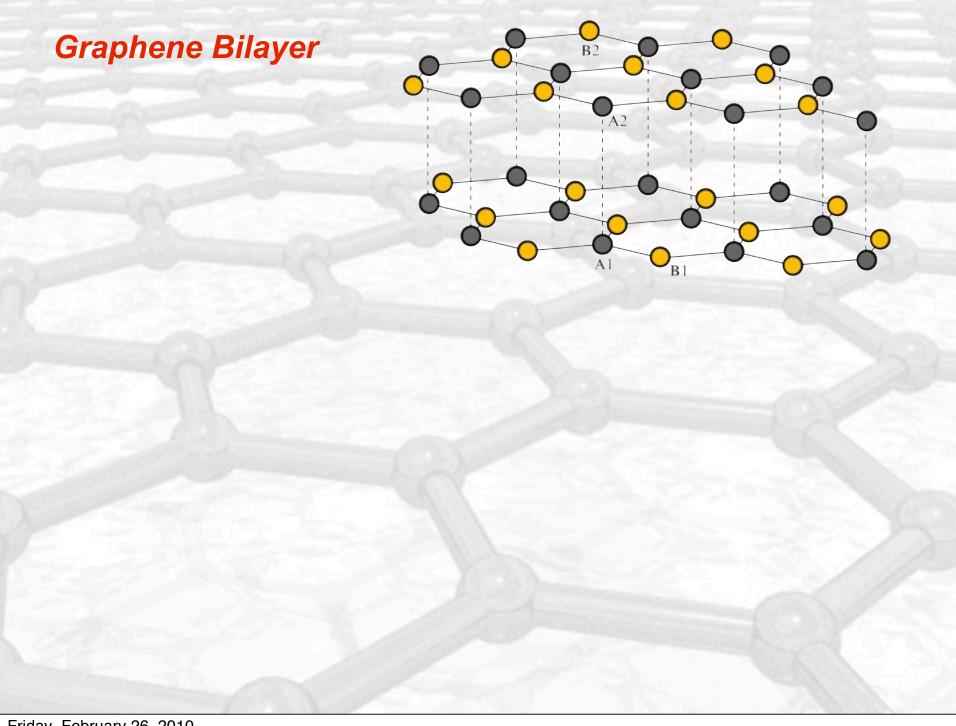
100-GHz Transistors from Wafer-Scale Epitaxial Graphene

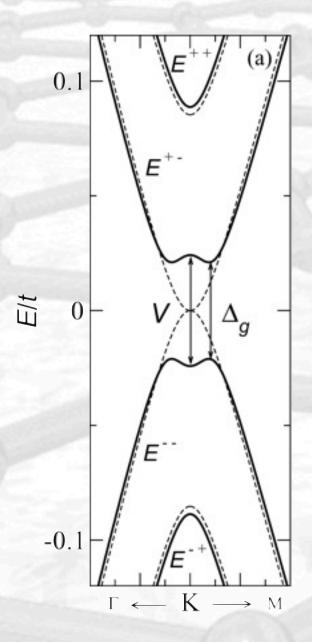
Y.-M. Lin,* C. Dimitrakopoulos, K. A. Jenkins, D. B. Farmer, H.-Y. Chiu,
A. Grill, Ph. Avouris*

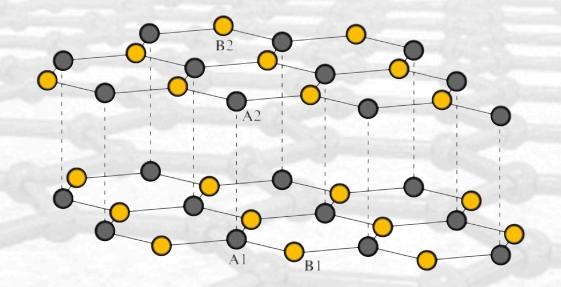
5 FEBRUARY 2010 VOL 327 SCIENCE

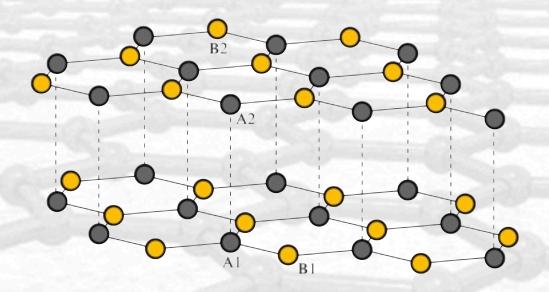


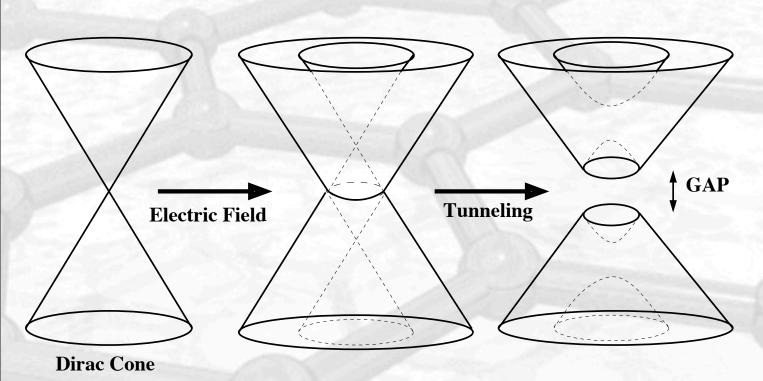




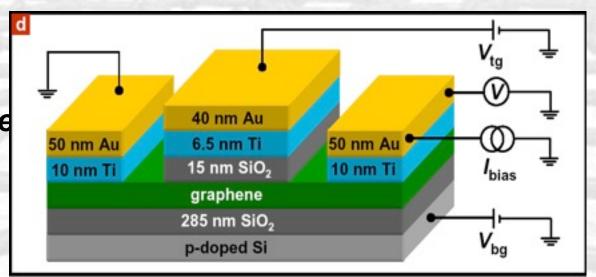


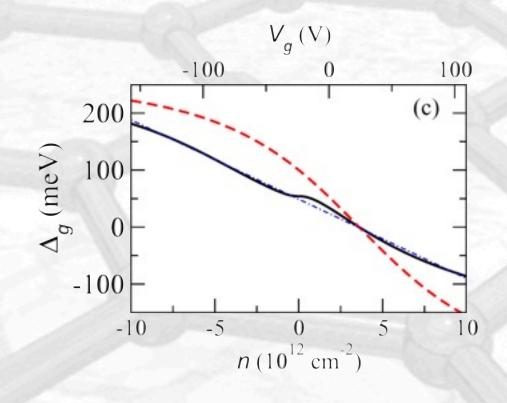




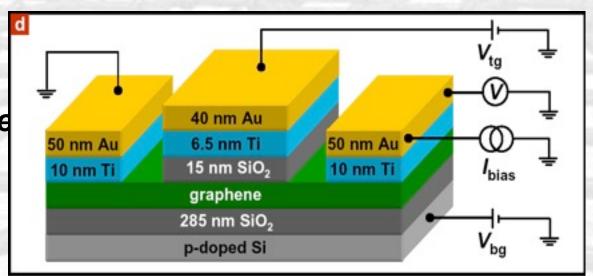


Semiconductor tunable by electric field effect





Semiconductor tunable by electric field effect

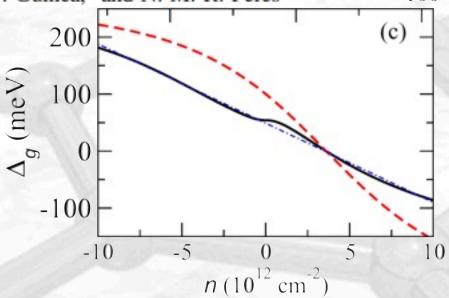


100

Electronic properties of bilaver and multilaver graphene

PHYSICAL REVIEW B 78, 045405 (2008)

Johan Nilsson, 1,2 A. H. Castro Neto, F. Guinea, and N. M. R. Peres

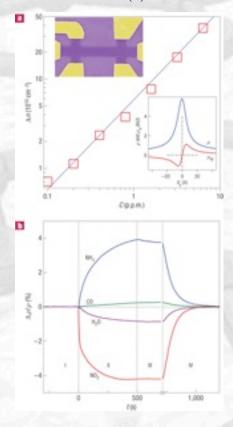




Hype or Hope?

Detection of individual gas molecules adsorbed on graphene F. Schedin, A. K. Geim, S. V. Morozov, E. W. Hill, P. Blake, M. I. Katsnelson & K. S. Novoselov

F. Schedin, A. K. Geim, S. V. Morozov, E. W. Hill, P. Blake, M. I. Katsnelson & K. S. Novoselov Nature Mater 6 (9): 652–655.

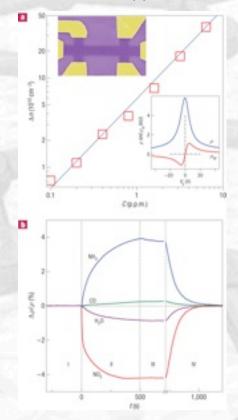


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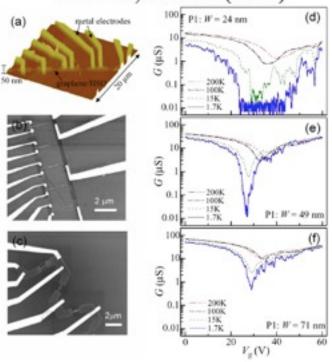
Nature Mater 6 (9): 652-655.

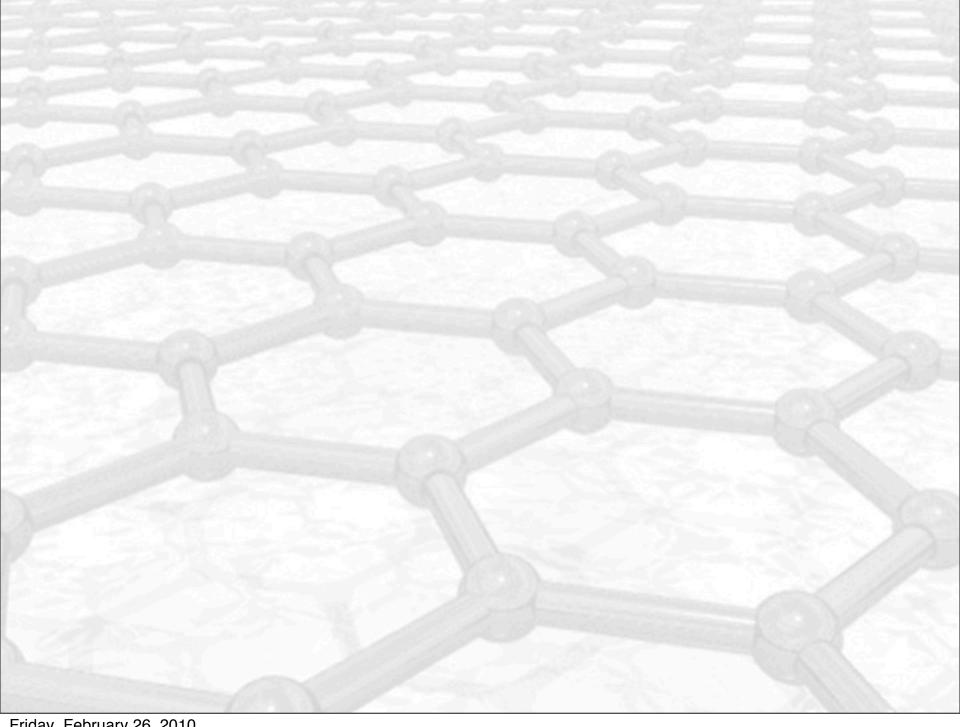


Energy Band-Gap Engineering of Graphene Nanoribbons

Melinda Y. Han, Barbaros Özvilmaz, Yuanbo Zhang, and Philip Kim²

PRL 98, 206805 (2007)

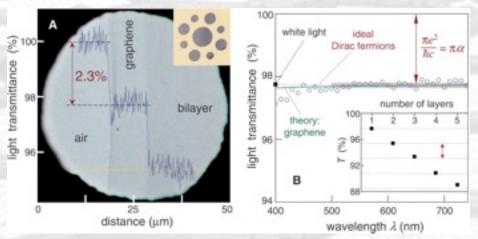




Friday, February 26, 2010

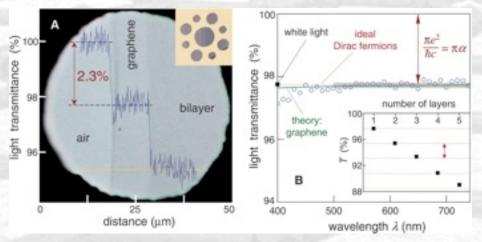
Fine Structure Constant Defines Visual Transparency of Graphene

R. R. Nair, P. Blake, A. N. Grigorenko, K. S. Novoselov, T. J. Booth, T. Stauber, N. M. R. Peres, A. K. Geim Science 320: 1308.



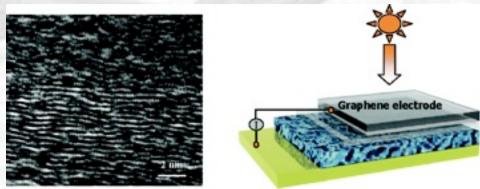
Fine Structure Constant Defines Visual Transparency of Graphene

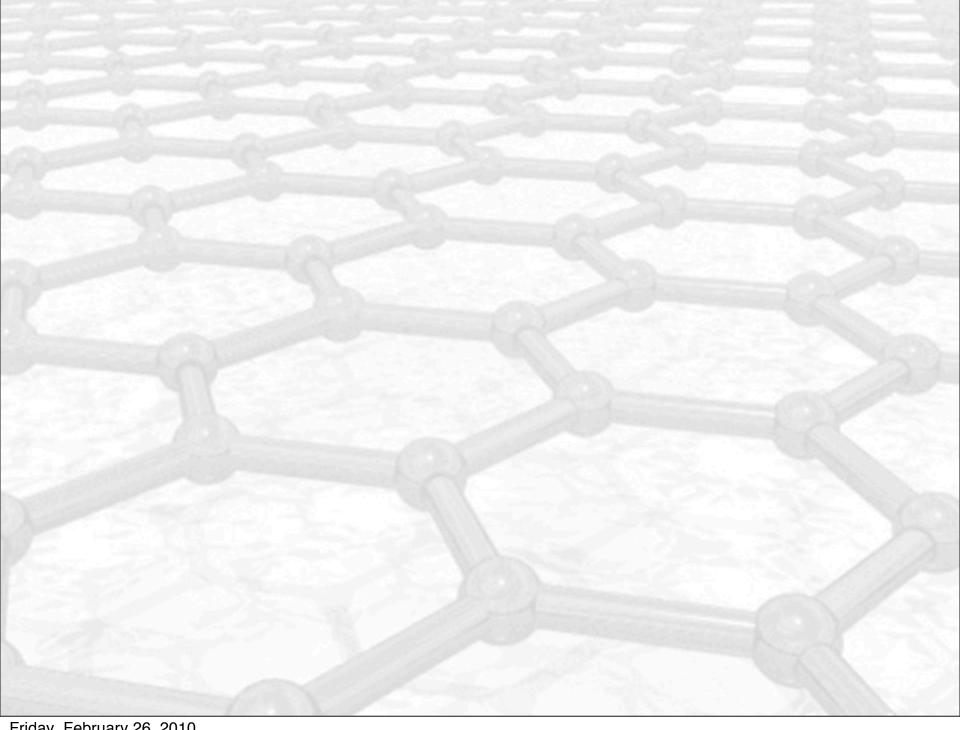
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Transparent, Conductive Graphene Electrodes for Dye-Sensitized Solar Cells

Xuan Wang, Linjie Zhi, and Klaus Müllen Nano Letters 8 (1): 323.

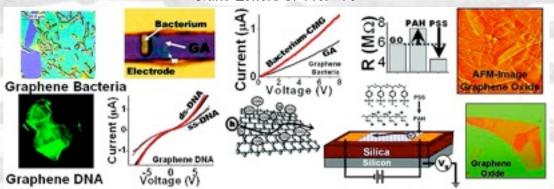




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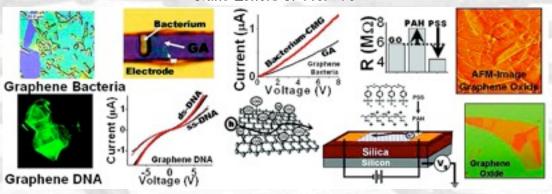
Graphene-Based Single-Bacterium Resolution Biodevice and DNA Transistor: Interfacing Graphene Derivatives with Nanoscale and Microscale Biocomponents

Nihar Mohanty and Vikas Berry *Nano Letters* **8**: 4469–76



Graphene-Based Single-Bacterium Resolution Biodevice and DNA Transistor: Interfacing Graphene Derivatives with Nanoscale and Microscale Biocomponents

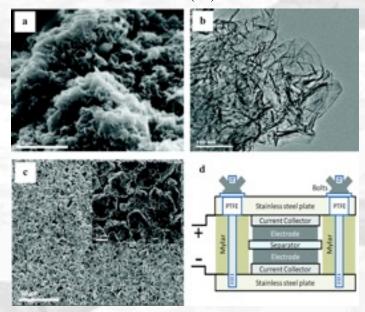
Nihar Mohanty and Vikas Berry *Nano Letters* **8**: 4469–76

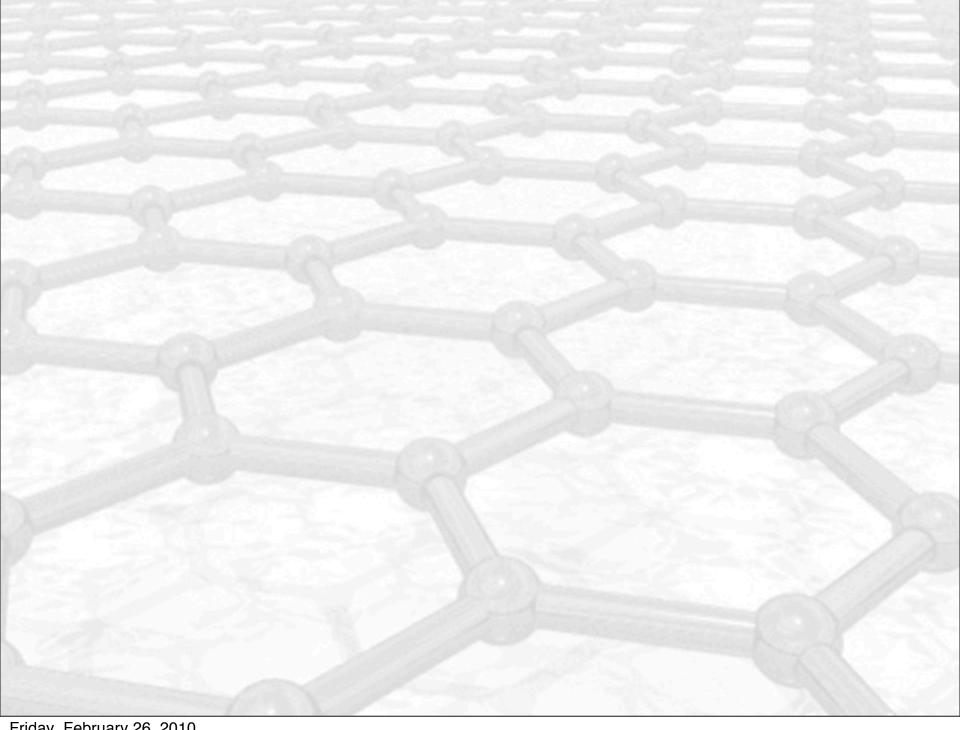


Graphene-Based Ultracapacitors

Meryl D. Stoller, Sungjin Park, Yanwu Zhu, Jinho An and Rodney S. Ruof

Nano Lett 8 (10): 3498.

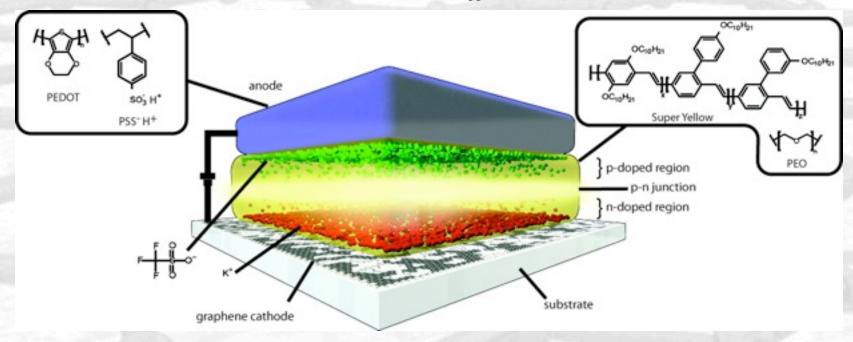




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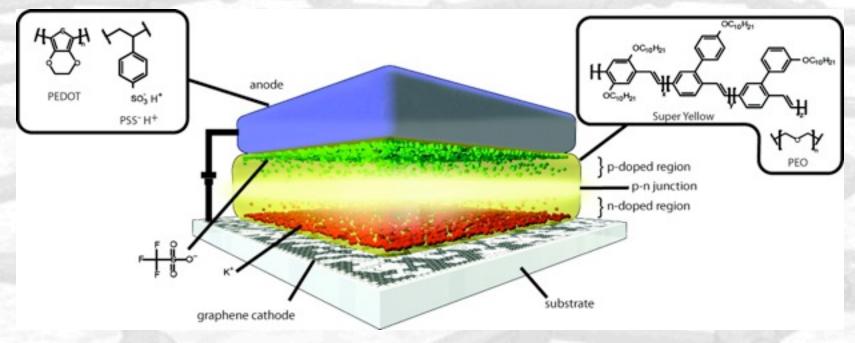
Graphene and Mobile Ions: The Key to All-Plastic,

Solution-Processed Light-Emitting DevicesPiotr Matyba, Hisato Yamaguchi, Goki Eda, Manish Chhowalla, Ludvig Edman and Nathaniel D. Robinson ACS Nano, 2010, 4 (2), pp 637–642



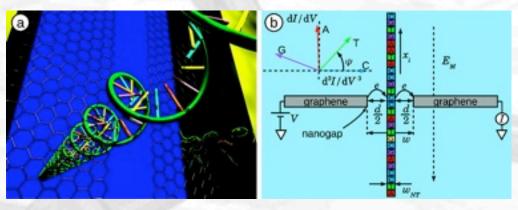
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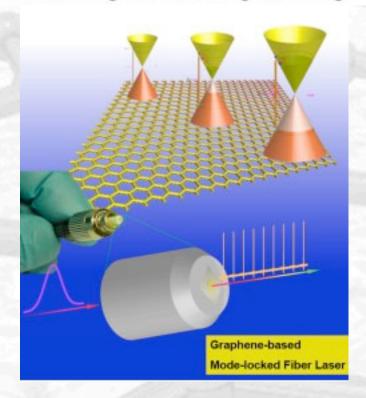
Rapid Sequencing of Individual DNA Molecules in Graphene Nanogaps

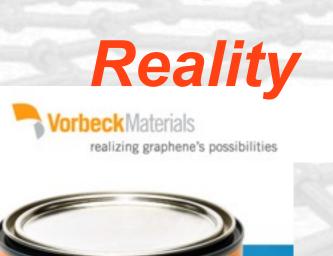
Henk W. Ch. Postma *Nano Lett.*, 2010, 10 (2), pp 420–425



Atomic-Layer Graphene as a Saturable Absorber for Ultrafast Pulsed Lasers Adv. Funct. Mater. 2009, 19, 3077–3083

By Qiaoliang Bao, Han Zhang, Yu Wang, Zhenhua Ni, Yongli Yan, Ze Xiang Shen, Kian Ping Loh,* and Ding Yuan Tang*







41

Future Directions for Graphene Research

Chemistry and Materials Science
Tailoring graphene's electronic properties:

Paper-cutting: Structural engineering

Decorating: Band structure engineering

Origami: Strain engineering

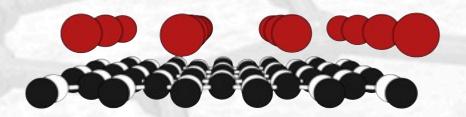
Future Directions for Graphene Research

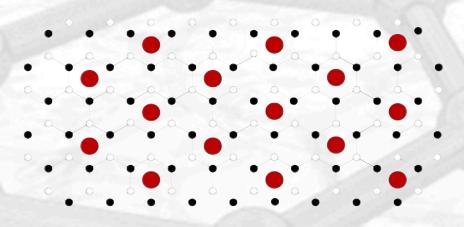
Chemistry and Materials Science Tailoring graphene's electronic properties:

Paper-cutting: Structural engineering

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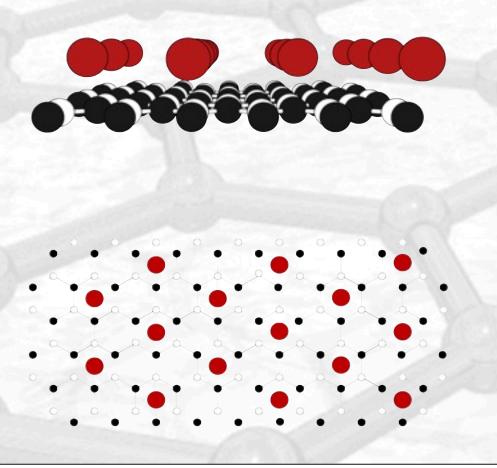
Future Directions for Graphene Research

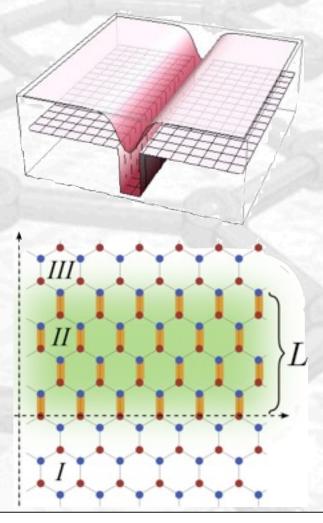
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The rise of graphene... Much more to come

